

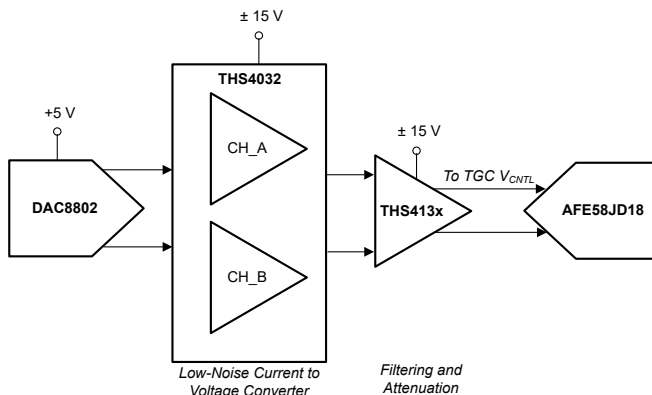
## 《THS413x 高速、低噪声、全差分 I/O 放大器》

### 1 特性

- 高性能
  - 带宽：170MHz (  $V_{CC} = \pm 15V$ ,  $G = 1V/V$  )
  - 压摆率：51 V/ $\mu$ s
  - 增益带宽积：215 MHz
  - 失真：-102dBc THD (  $2V_{PP}$ 、250kHz 时 )
- 电压噪声
  - 1/f 电压噪声拐角频率：350 Hz
  - 输入基准噪声 1.25nV/  $\sqrt{Hz}$
- 单电源工作电压范围：5 V 至 30 V
- 静态电流 ( 关断 )：860 $\mu$ A (THS4130)
- 温度范围：-40°C 至 +85°C
- 封装：PowerPAD™ HVSSOP-8、SOIC-8、VSSOP-8

### 2 应用

- 单端至差分转换
- 差分 ADC 驱动器
- 差分抗混叠
- 差分发送器和接收器
- 输出电平转换器
- 医疗超声波



适用于超声波的  
时间增益控制 DAC 参考设计

### 3 说明

THS4130 和 THS4131 器件 (THS413x) 是使用德州仪器 (TI) 先进的高压互补双极工艺制造的全差分输入/输出放大器系列。

THS413x 使用从输入到输出的真正全差分信号路径，提供高达  $\pm 15V$  的高电源电压。这种设计带来了出色的共模噪声抑制能力 (800kHz 时为 95dB) 和总谐波失真 (  $2V_{PP}$ 、250kHz 时为 -102dBc )。高电压差分信号链可通过宽电源电压范围提高裕量和动态范围，而无需为差分信号的每个极性添加单独的放大器。

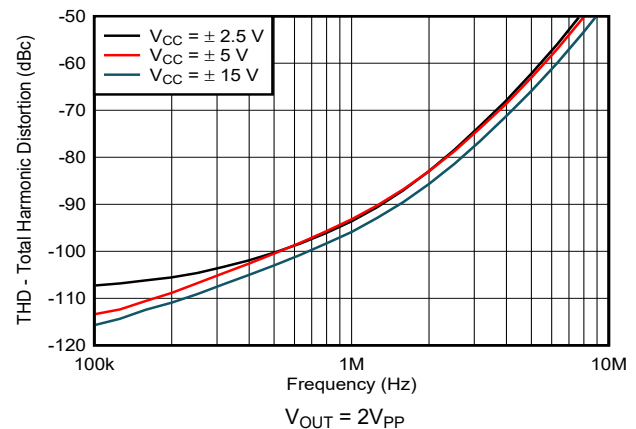
THS413x 具有 -40°C 至 +85°C 的宽额定运行温度范围。

#### 器件信息

| 器件型号 <sup>(1)</sup> | 关断引脚 | 封装 <sup>(2)</sup>                                             |
|---------------------|------|---------------------------------------------------------------|
| THS4130             | 是    | D ( SOIC , 8 ) 、<br>DGK ( VSSOP , 8 ) 、<br>DGN ( HVSSOP , 8 ) |
| THS4131             | 否    |                                                               |

(1) 请参阅 [器件比较表](#)。

(2) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



总谐波失真与频率间的关系



## Table of Contents

|                                                |           |                                                                  |           |
|------------------------------------------------|-----------|------------------------------------------------------------------|-----------|
| <b>1 特性</b> .....                              | <b>1</b>  | 8.3 Feature Description.....                                     | <b>12</b> |
| <b>2 应用</b> .....                              | <b>1</b>  | 8.4 Device Functional Modes.....                                 | <b>13</b> |
| <b>3 说明</b> .....                              | <b>1</b>  | <b>9 Application and Implementation</b> .....                    | <b>14</b> |
| <b>4 Revision History</b> .....                | <b>2</b>  | 9.1 Application Information.....                                 | <b>14</b> |
| <b>5 Device Comparison Table</b> .....         | <b>3</b>  | 9.2 Typical Application.....                                     | <b>17</b> |
| <b>6 Pin Configuration and Functions</b> ..... | <b>3</b>  | 9.3 Power Supply Recommendations.....                            | <b>18</b> |
| <b>7 Specifications</b> .....                  | <b>4</b>  | 9.4 Layout.....                                                  | <b>19</b> |
| 7.1 Absolute Maximum Ratings.....              | <b>4</b>  | <b>10 Device and Documentation Support</b> .....                 | <b>22</b> |
| 7.2 ESD Ratings.....                           | <b>4</b>  | 10.1 Documentation Support.....                                  | <b>22</b> |
| 7.3 Recommended Operating Conditions.....      | <b>4</b>  | 10.2 接收文档更新通知.....                                               | <b>22</b> |
| 7.4 Thermal Information.....                   | <b>4</b>  | 10.3 支持资源.....                                                   | <b>22</b> |
| 7.5 Electrical Characteristics.....            | <b>5</b>  | 10.4 Trademarks.....                                             | <b>22</b> |
| 7.6 Typical Characteristics.....               | <b>7</b>  | 10.5 静电放电警告.....                                                 | <b>22</b> |
| <b>8 Detailed Description</b> .....            | <b>12</b> | 10.6 术语表.....                                                    | <b>22</b> |
| 8.1 Overview.....                              | <b>12</b> | <b>11 Mechanical, Packaging, and Orderable Information</b> ..... | <b>22</b> |
| 8.2 Functional Block Diagram.....              | <b>12</b> |                                                                  |           |

## 4 Revision History

注：以前版本的页码可能与当前版本的页码不同

| <b>Changes from Revision K (August 2022) to Revision L (August 2023)</b>                                                                                                                                                                                                                                                                                            | <b>Page</b> |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------|
| • Changed MSOP and MSOP-PowerPad to VSSOP and HVSSOP in Thermal Information table.....                                                                                                                                                                                                                                                                              | <b>4</b>    |
| • Changed thermal specifications for DGN package in <i>Thermal Information</i> table.....                                                                                                                                                                                                                                                                           | <b>4</b>    |
| • Changed the Electrical Characteristics section to combine both Electrical Characteristics tables into one table with improved small-signal bandwidth, slew rate, settling time, total harmonic distortion (THD), spurious-free dynamic range (SFDR), voltage noise, offset voltage drift, output swing, and quiescent current parameters for the DGN package..... | <b>5</b>    |
| • Changed input current noise typical from 1.3 pA/√Hz to 1.7 pA/√Hz for DGN package.....                                                                                                                                                                                                                                                                            | <b>5</b>    |
| • Changed common-mode input offset voltage maximum from 3.5 mV to 5.5 mV for DGN package.....                                                                                                                                                                                                                                                                       | <b>5</b>    |
| • Changed maximum input bias current from 6 μA to 15.4 μA for DGN package.....                                                                                                                                                                                                                                                                                      | <b>5</b>    |
| • Changed single input resistance parameter into separate common-mode and differential input resistance parameters for DGN package.....                                                                                                                                                                                                                             | <b>5</b>    |
| • Changed <i>Typical Characteristics: THS413xD, THS413xDGK</i> title to <i>Typical Characteristics</i> and deleted obsolete <i>Typical Characteristics: THS413xDGN</i> section; all plots now in one section.....                                                                                                                                                   | <b>7</b>    |

| <b>Changes from Revision J (March 2022) to Revision K (August 2022)</b>                                                         | <b>Page</b> |
|---------------------------------------------------------------------------------------------------------------------------------|-------------|
| • Updated thermal specifications for DGK package in <i>Thermal Information</i> table.....                                       | <b>4</b>    |
| • Changed title of <i>Electrical Characteristics: THS413xD</i> to <i>Electrical Characteristics: THS413xD, THS413xDGK</i> ..... | <b>5</b>    |
| • Changed title of <i>Typical Characteristics: THS413xD</i> to <i>Typical Characteristics: THS413xD, THS413xDGK</i> .....       | <b>7</b>    |

## 5 Device Comparison Table

| T <sub>A</sub>  | D (SOIC, 8) | DGK (VSSOP, 8) | DGN (HVSSOP, 8) |
|-----------------|-------------|----------------|-----------------|
| 0°C to +70°C    | THS4130CD   | THS4130CDGK    | THS4130CDGN     |
|                 | THS4131CD   | THS4131CDGK    | THS4131CDGN     |
| - 40°C to +85°C | THS4130ID   | THS4130IDGK    | THS4130IDGN     |
|                 | THS4131ID   | THS4131IDGK    | THS4131IDGN     |

## 6 Pin Configuration and Functions

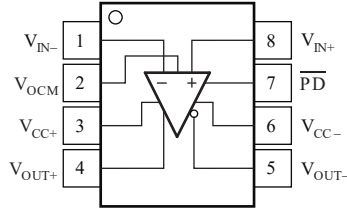


图 6-1. D Package, 8-Pin SOIC,  
DGK Package, 8-pin VSSOP,  
DGN Package, 8-Pin HVSSOP  
THS4130 (Top View)

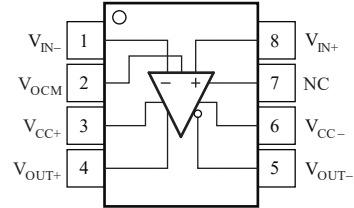


图 6-2. D Package, 8-Pin SOIC,  
DGK Package, 8-pin VSSOP,  
DGN Package, 8-Pin HVSSOP  
THS4131 (Top View)

表 6-1. Pin Functions

| PIN               |             | NO.         | TYPE <sup>(1)</sup> | DESCRIPTION                                                                                                                                                                                                                      |
|-------------------|-------------|-------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| NAME              | THS4130     | THS4131     |                     |                                                                                                                                                                                                                                  |
| NC                | —           | 7           | —                   | No connect                                                                                                                                                                                                                       |
| PD                | 7           | —           | I                   | Active low power-down pin                                                                                                                                                                                                        |
| V <sub>CC+</sub>  | 3           | 3           | I/O                 | Positive supply voltage pin                                                                                                                                                                                                      |
| V <sub>CC-</sub>  | 6           | 6           | I/O                 | Negative supply voltage pin                                                                                                                                                                                                      |
| V <sub>IN-</sub>  | 1           | 1           | I                   | Negative input pin                                                                                                                                                                                                               |
| V <sub>OCM</sub>  | 2           | 2           | I                   | Common mode input pin                                                                                                                                                                                                            |
| V <sub>OUT+</sub> | 4           | 4           | O                   | Positive output pin                                                                                                                                                                                                              |
| V <sub>OUT-</sub> | 5           | 5           | O                   | Negative output pin                                                                                                                                                                                                              |
| V <sub>IN+</sub>  | 8           | 8           | I                   | Positive input pin                                                                                                                                                                                                               |
| Thermal Pad       | Thermal Pad | Thermal Pad | —                   | Thermal pad. DGN (HVSSOP) package only. For the best thermal performance, connect the thermal pad to a large copper plane. This pad is electrically isolated from the die so the pad can be connected to any pin on the package. |

(1) I = input, O = output.

## 7 Specifications

### 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

|                        |                                                                                  | MIN       | MAX       | UNIT       |
|------------------------|----------------------------------------------------------------------------------|-----------|-----------|------------|
| $V_I$                  | Input voltage                                                                    | $-V_{CC}$ | $+V_{CC}$ | V          |
| $V_{CC-}$ to $V_{CC+}$ | Supply voltage                                                                   |           | 33        | V          |
|                        | Supply turn on and turn off $dV/dt$ <sup>(2)</sup>                               |           | 1.7       | V/ $\mu$ s |
| $I_O$                  | Output current <sup>(3)</sup>                                                    |           | 150       | mA         |
| $V_{ID}$               | Differential input voltage                                                       | -1.5      | 1.5       | V          |
| $I_{IN}$               | Continuous input current                                                         |           | 10        | mA         |
| $T_J$                  | Junction temperature                                                             |           | 150       | °C         |
|                        | Junction temperature, continuous operation, long-term reliability <sup>(4)</sup> |           | 125       | °C         |
| $T_A$                  | Ambient temperature                                                              | C-suffix  | 0         | °C         |
|                        |                                                                                  | I-suffix  | -40       | °C         |
| $T_{stg}$              | Storage temperature                                                              | -65       | 150       | °C         |

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Stay below this specification to make sure that the edge-triggered ESD absorption devices across the supply pins remain off.
- (3) Some of the THS413x packages incorporate a thermal pad on the underside of the chip. This thermal pad acts as a heat sink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so can result in exceeding the maximum junction temperature which can permanently damage the device. See TI technical briefs [SLMA002](#) and [SLMA004](#) for more information about using the PowerPAD integrated circuit package.
- (4) The maximum junction temperature for continuous operation is limited by package constraints. Operation greater than this temperature can result in reduced reliability, reduced lifetime of the device, or both.

### 7.2 ESD Ratings

|             |                         |                                                                       | VALUE      | UNIT |
|-------------|-------------------------|-----------------------------------------------------------------------|------------|------|
| $V_{(ESD)}$ | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>     | $\pm 2500$ | V    |
|             |                         | Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup> | $\pm 1500$ |      |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|          |                                |                 | MIN       | NOM | MAX      | UNIT |
|----------|--------------------------------|-----------------|-----------|-----|----------|------|
| $V_{CC}$ | Supply voltage                 | Dual supply     | $\pm 2.5$ |     | $\pm 15$ | V    |
|          |                                | Single supply   | 5         |     | 30       |      |
| $T_A$    | Operating free-air temperature | C-suffix device | 0         |     | 70       | °C   |
|          |                                | I-suffix device | -40       |     | 85       |      |

### 7.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |                                              | THS413x  |             |              | UNIT |
|-------------------------------|----------------------------------------------|----------|-------------|--------------|------|
|                               |                                              | D (SOIC) | DGK (VSSOP) | DGN (HVSSOP) |      |
|                               |                                              | 8 PINS   | 8 PINS      | 8 PINS       |      |
| $R_{JA}$                      | Junction-to-ambient thermal resistance       | 126.3    | 147.3       | 57.6         | °C/W |
| $R_{JC(top)}$                 | Junction-to-case (top) thermal resistance    | 67.3     | 37.9        | 76.3         | °C/W |
| $R_{JB}$                      | Junction-to-board thermal resistance         | 69.8     | 83.2        | 30.0         | °C/W |
| $\psi_{JT}$                   | Junction-to-top characterization parameter   | 19.5     | 0.9         | 4.0          | °C/W |
| $\psi_{JB}$                   | Junction-to-board characterization parameter | 69.0     | 81.6        | 29.9         | °C/W |

| THERMAL METRIC <sup>(1)</sup> |                                              | THS413x  |             |              | UNIT |
|-------------------------------|----------------------------------------------|----------|-------------|--------------|------|
|                               |                                              | D (SOIC) | DGK (VSSOP) | DGN (HVSSOP) |      |
|                               |                                              | 8 PINS   | 8 PINS      | 8 PINS       |      |
| R <sub>JC(bot)</sub>          | Junction-to-case (bottom) thermal resistance | N/A      | N/A         | 14.3         | °C/W |

(1) For information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

## 7.5 Electrical Characteristics

at V<sub>CC</sub> = ±5 V, gain = 1 V/V, R<sub>F</sub> = 390 Ω, R<sub>L</sub> = 800 Ω, and T<sub>A</sub> = +25°C (unless otherwise noted)

| PARAMETER              |                                  | TEST CONDITIONS                                                                                                   |                              | MIN | TYP   | MAX      | UNIT |
|------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------|------------------------------|-----|-------|----------|------|
| DYNAMIC PERFORMANCE    |                                  |                                                                                                                   |                              |     |       |          |      |
| SSBW                   | Small-signal bandwidth ( - 3 dB) | V <sub>I</sub> = 63 mV <sub>PP</sub> , gain = 1, R <sub>F</sub> = 390 Ω , single-ended input, differential output | V <sub>CC</sub> = 5 V        |     | 165   | MHz      |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±5 V       |     | 166   |          |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±15 V      |     | 170   |          |      |
|                        |                                  | V <sub>I</sub> = 63 mV <sub>PP</sub> , gain = 2, R <sub>F</sub> = 750 Ω , single-ended input, differential output | V <sub>CC</sub> = 5 V        |     | 97    |          |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±5 V       |     | 98    |          |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±15 V      |     | 100   |          |      |
| SR                     | Slew rate <sup>(2)</sup>         |                                                                                                                   |                              |     | 67    | V/μs     |      |
| t <sub>s</sub>         | Settling time                    | To 0.1%                                                                                                           | Step voltage = 2 V, gain = 1 |     | 39    | ns       |      |
|                        |                                  | To 0.01%                                                                                                          | Step voltage = 2 V, gain = 1 |     | 61    |          |      |
| DISTORTION PERFORMANCE |                                  |                                                                                                                   |                              |     |       |          |      |
| THD                    | Total harmonic distortion        | V <sub>CC</sub> = 5 V, V <sub>O</sub> = 2 V <sub>PP</sub> , differential input/output                             | f = 250 kHz                  |     | - 101 | dBc      |      |
|                        |                                  |                                                                                                                   | f = 1 MHz                    |     | - 87  |          |      |
|                        |                                  | V <sub>CC</sub> = ±5 V, V <sub>O</sub> = 2 V <sub>PP</sub> , differential input/output                            | f = 250 kHz                  |     | - 100 |          |      |
|                        |                                  |                                                                                                                   | f = 1 MHz                    |     | - 87  |          |      |
|                        |                                  | V <sub>CC</sub> = ±15 V, V <sub>O</sub> = 2 V <sub>PP</sub> , differential input/output                           | f = 250 kHz                  |     | - 102 |          |      |
|                        |                                  |                                                                                                                   | f = 1 MHz                    |     | - 88  |          |      |
|                        |                                  | V <sub>CC</sub> = ±5 V, V <sub>O</sub> = 4 V <sub>PP</sub> , differential input/output                            | f = 250 kHz                  |     | - 94  |          |      |
|                        |                                  |                                                                                                                   | f = 1 MHz                    |     | - 79  |          |      |
|                        |                                  | V <sub>CC</sub> = ±15 V, V <sub>O</sub> = 4 V <sub>PP</sub> , differential input/output                           | f = 250 kHz                  |     | - 95  |          |      |
|                        |                                  |                                                                                                                   | f = 1 MHz                    |     | - 80  |          |      |
| SFDR                   | Spurious-free dynamic range      | V <sub>O</sub> = 2 V <sub>PP</sub> , f = 250 kHz, differential input/output                                       | V <sub>CC</sub> = ±2.5       |     | 103   | dBc      |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±5         |     | 106   |          |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±15        |     | 108   |          |      |
|                        |                                  | V <sub>O</sub> = 4 V <sub>PP</sub> , f = 250 kHz, differential input/output                                       | V <sub>CC</sub> = ±5         |     | 98    |          |      |
|                        |                                  |                                                                                                                   | V <sub>CC</sub> = ±15        |     | 100   |          |      |
| IMD3                   | Third intermodulation distortion | V <sub>I(PP)</sub> = 4 V, F <sub>1</sub> = 3 MHz, F <sub>2</sub> = 3.5 MHz                                        |                              |     | - 53  | dBc      |      |
| OIP3                   | Third-order intercept            | V <sub>I(PP)</sub> = 4 V, F <sub>1</sub> = 3 MHz, F <sub>2</sub> = 3.5 MHz                                        |                              |     | 41.5  | dB       |      |
| NOISE PERFORMANCE      |                                  |                                                                                                                   |                              |     |       |          |      |
| V <sub>n</sub>         | Input voltage noise              | f = 10 kHz                                                                                                        |                              |     | 1.25  | nV/ √ Hz |      |
| I <sub>n</sub>         | Input current noise              | f = 10 kHz                                                                                                        |                              |     | 1.7   | pA/ √ Hz |      |
| DC PERFORMANCE         |                                  |                                                                                                                   |                              |     |       |          |      |
| A <sub>OL</sub>        | Open-loop gain                   | T <sub>A</sub> = 25°C                                                                                             |                              |     | 71    | 78       | dB   |
|                        |                                  | T <sub>A</sub> = full range                                                                                       |                              |     | 69    |          |      |
| V <sub>OS</sub>        | Input offset voltage             | T <sub>A</sub> = 25°C                                                                                             |                              |     | ±0.2  | 2        | mV   |
|                        |                                  | T <sub>A</sub> = full range <sup>(1)</sup>                                                                        |                              |     |       | 3        |      |

## 7.5 Electrical Characteristics (续)

at  $V_{CC} = \pm 5\text{ V}$ , gain = 1 V/V,  $R_F = 390\ \Omega$ ,  $R_L = 800\ \Omega$ , and  $T_A = +25^\circ\text{C}$  (unless otherwise noted)

| PARAMETER              |                                             | TEST CONDITIONS                                |                                            | MIN           | TYP        | MAX  | UNIT  |
|------------------------|---------------------------------------------|------------------------------------------------|--------------------------------------------|---------------|------------|------|-------|
|                        | Common-mode input offset voltage            | Referred to V <sub>OCM</sub>                   |                                            |               | 0.2        | 5.5  | mV    |
|                        | Input offset voltage drift                  | T <sub>A</sub> = full range <sup>(1)</sup>     |                                            |               | 2          |      | μV/°C |
| I <sub>IB</sub>        | Input bias current                          | T <sub>A</sub> = full range <sup>(1)</sup>     |                                            |               | 5          | 15.4 | μA    |
| I <sub>OS</sub>        | Input offset current                        | T <sub>A</sub> = full range <sup>(1)</sup>     |                                            |               | 100        | 500  | nA    |
|                        | Input offset current drift                  |                                                |                                            |               | 1          |      | nA/°C |
| INPUT CHARACTERISTICS  |                                             |                                                |                                            |               |            |      |       |
| CMRR                   | Common-mode rejection ratio                 | T <sub>A</sub> = full range <sup>(1)</sup>     |                                            | 80            | 95         |      | dB    |
| V <sub>ICM</sub>       | Common-mode input voltage                   |                                                |                                            | - 3.77 to 4.3 | - 4 to 4.5 |      | V     |
| R <sub>I_CM</sub>      | Common-mode input resistance                | Measured into each input pin                   |                                            |               | 215        |      | M Ω   |
| R <sub>I_DIFF</sub>    | Differential input resistance               | Measured into each input pin                   |                                            |               | 10         |      | k Ω   |
| C <sub>I_CM</sub>      | Common-mode input capacitance               | Measured into each input pin, closed loop      |                                            |               | 1.4        |      | pF    |
| C <sub>I_DIFF</sub>    | Differential input capacitance              | Measured into each input pin, closed loop      |                                            |               | 2.5        |      |       |
| OUTPUT CHARACTERISTICS |                                             |                                                |                                            |               |            |      |       |
| R <sub>O</sub>         | Output resistance                           | Open loop                                      |                                            |               | 41         |      | Ω     |
|                        | Output voltage swing                        | V <sub>CC</sub> = 5 V, R <sub>L</sub> = 1 kΩ   | T <sub>A</sub> = 25°C                      | 1.2 to 3.8    | 0.9 to 4.1 |      | V     |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | 1.3 to 3.7    | ±4         |      |       |
|                        |                                             | V <sub>CC</sub> = ±5 V, R <sub>L</sub> = 1 kΩ  | T <sub>A</sub> = 25°C                      | ±3.7          |            |      |       |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | ±3.6          |            |      |       |
|                        |                                             | V <sub>CC</sub> = ±15 V, R <sub>L</sub> = 1 kΩ | T <sub>A</sub> = 25°C                      | ±11.5         | ±12.4      |      |       |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | ±11.2         |            |      |       |
| I <sub>O</sub>         | Output current                              | V <sub>CC</sub> = 5 V, R <sub>L</sub> = 7 Ω    | T <sub>A</sub> = 25°C                      | 25            | 45         |      | mA    |
|                        |                                             |                                                | T <sub>A</sub> = full range                | 20            |            |      |       |
|                        |                                             | V <sub>CC</sub> = ±5 V, R <sub>L</sub> = 7 Ω   | T <sub>A</sub> = 25°C                      | 30            | 55         |      |       |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | 28            |            |      |       |
|                        |                                             | V <sub>CC</sub> = ±15 V, R <sub>L</sub> = 7 Ω  | T <sub>A</sub> = 25°C                      | 65            | 85         |      |       |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | 60            |            |      |       |
| POWER SUPPLY           |                                             |                                                |                                            |               |            |      |       |
| I <sub>CC</sub>        | Quiescent current                           | V <sub>CC</sub> = ±5 V                         | T <sub>A</sub> = 25°C                      | 10.4          | 15         |      | mA    |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> |               | 16         |      |       |
|                        |                                             | V <sub>CC</sub> = ±15 V                        | T <sub>A</sub> = 25°C                      | 13            |            |      |       |
| I <sub>CC(SD)</sub>    | Quiescent current (shutdown) (THS4130 only) | PD = - 5 V                                     | T <sub>A</sub> = 25°C                      | 0.86          | 1.4        |      | mA    |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> |               | 1.5        |      |       |
| PSRR                   | Power-supply rejection ratio (dc)           |                                                | T <sub>A</sub> = +25°C                     | 73            | 98         |      | dB    |
|                        |                                             |                                                | T <sub>A</sub> = full range <sup>(1)</sup> | 70            |            |      |       |

(1) The full range temperature is  $0^\circ\text{C}$  to  $+70^\circ\text{C}$  for the C-suffix device, and  $-40^\circ\text{C}$  to  $+85^\circ\text{C}$  for the I-suffix device.

(2) Slew rate is measured from an output level range of 25% to 75%.

## 7.6 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} = \pm 5\text{ V}$ ,  $R_F = 390\ \Omega$ , gain = +1 V/V, differential input, differential output, and  $R_L = 800\ \Omega$  (unless otherwise noted)

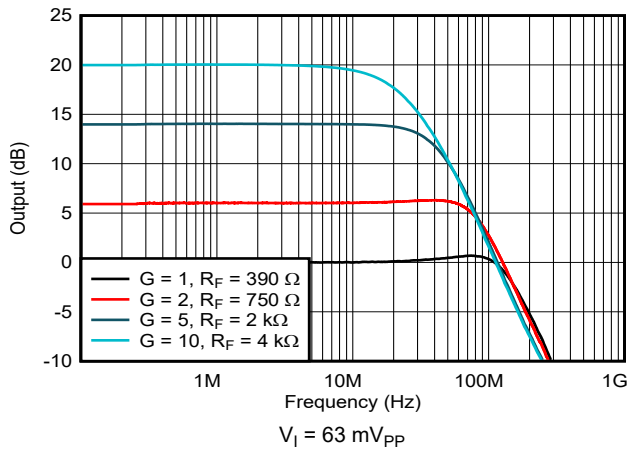


图 7-1. Small-Signal Frequency Response

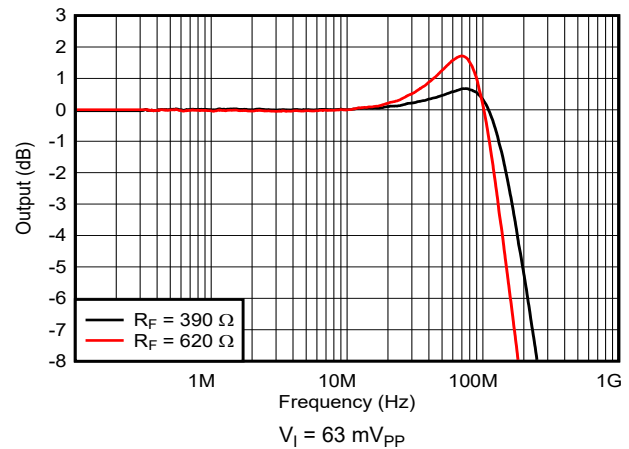


图 7-2. Small-Signal Frequency Response

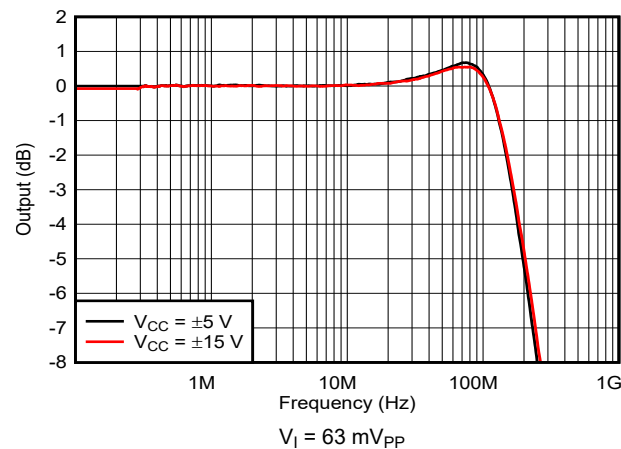


图 7-3. Small-Signal Frequency Response

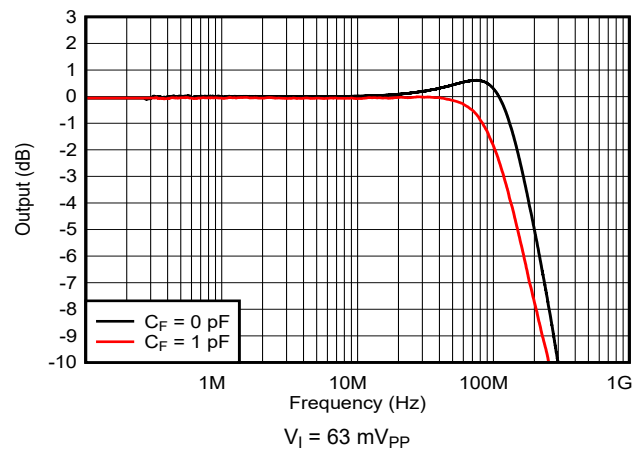


图 7-4. Small-Signal Frequency Response

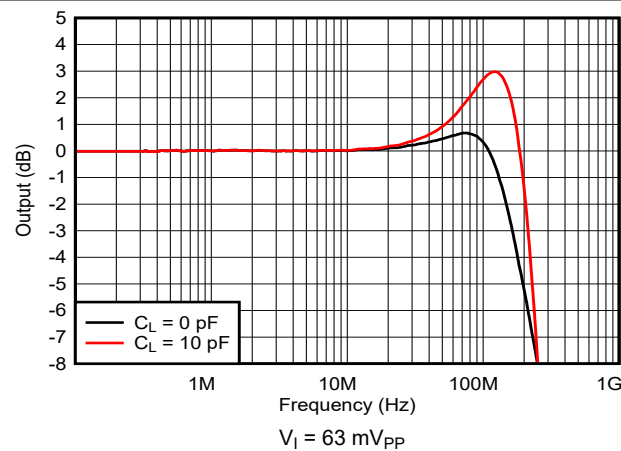


图 7-5. Small-Signal Frequency Response

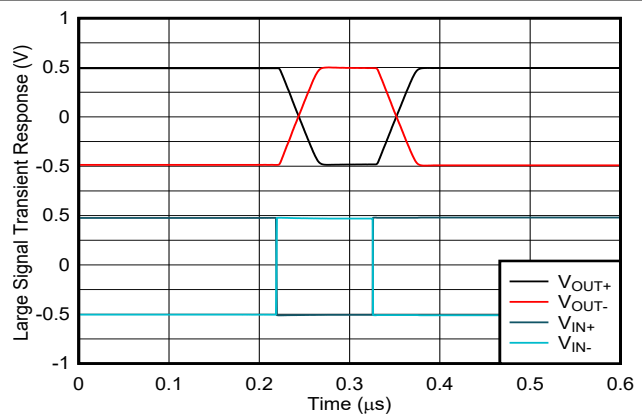


图 7-6. Large-Signal Transient Response (Differential In/Single Out)

## 7.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} = \pm 5\text{ V}$ ,  $R_F = 390\ \Omega$ , gain = +1 V/V, differential input, differential output, and  $R_L = 800\ \Omega$  (unless otherwise noted)

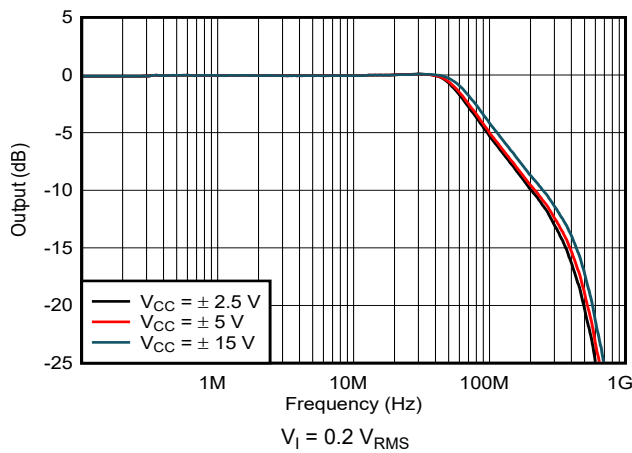


图 7-7. Large-Signal Frequency Response

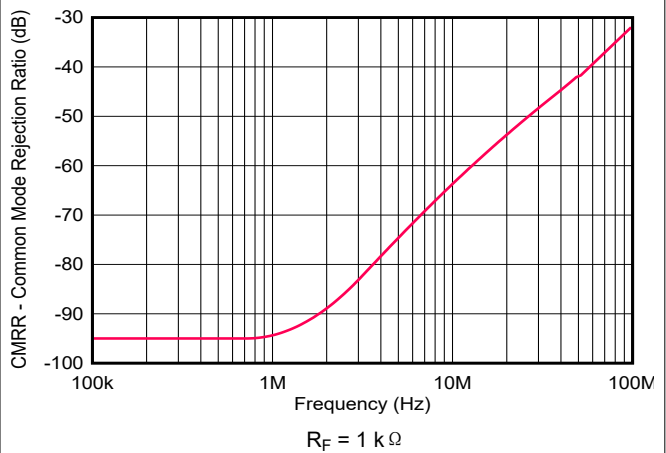


图 7-8. Common-Mode Rejection Ratio vs Frequency

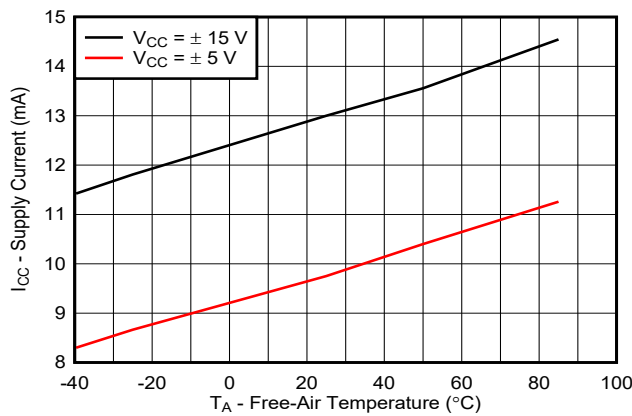


图 7-9. Supply Current vs Free-Air Temperature

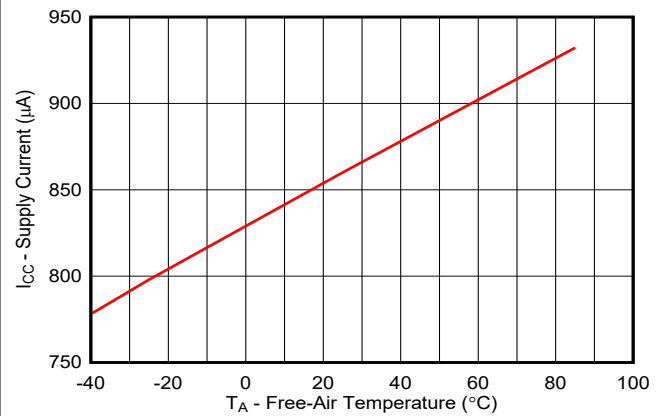


图 7-10. Supply Current vs Free-Air Temperature (Shutdown State)

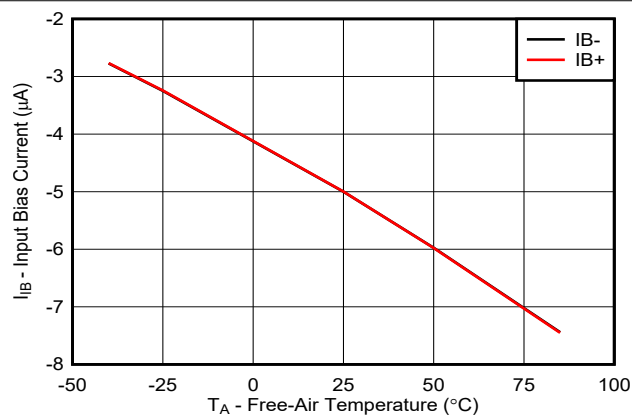


图 7-11. Input Bias Current vs Free-Air Temperature

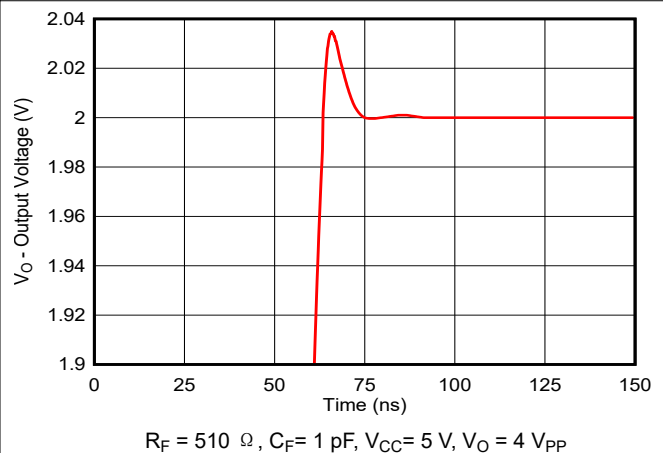


图 7-12. Settling Time



## 7.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} = \pm 5\text{ V}$ ,  $R_F = 390\ \Omega$ , gain = +1 V/V, differential input, differential output, and  $R_L = 800\ \Omega$  (unless otherwise noted)

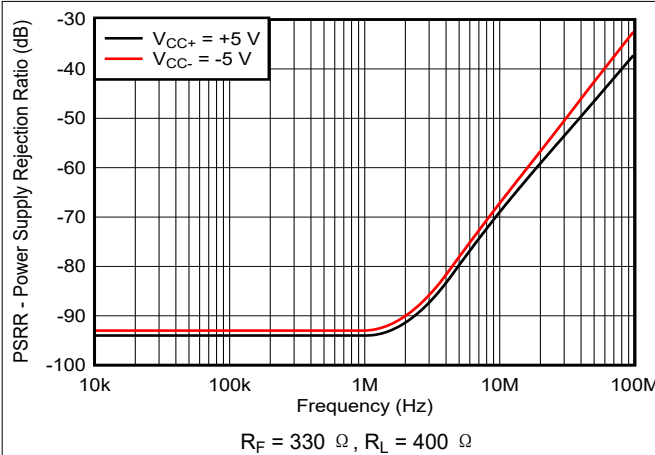


图 7-13. Power-Supply Rejection Ratio vs Frequency (Differential Out)

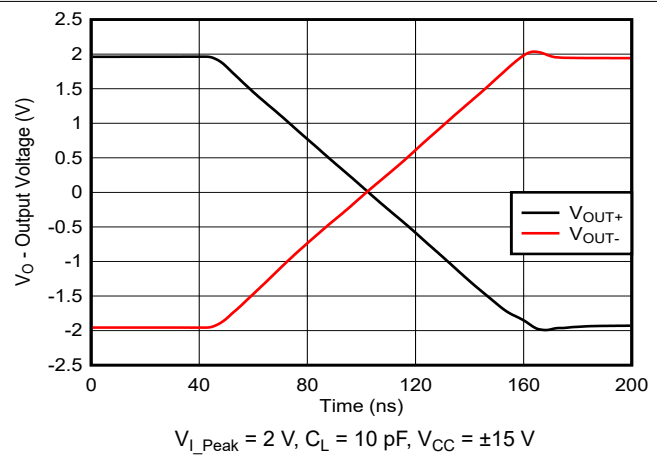


图 7-14. Large-Signal Transient Response

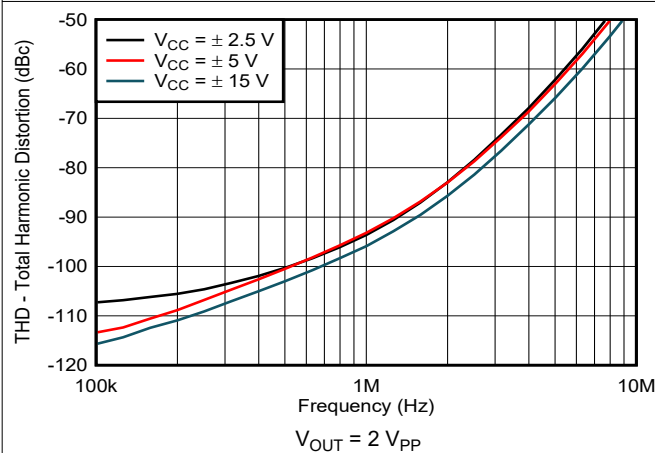


图 7-15. Total Harmonic Distortion vs Frequency

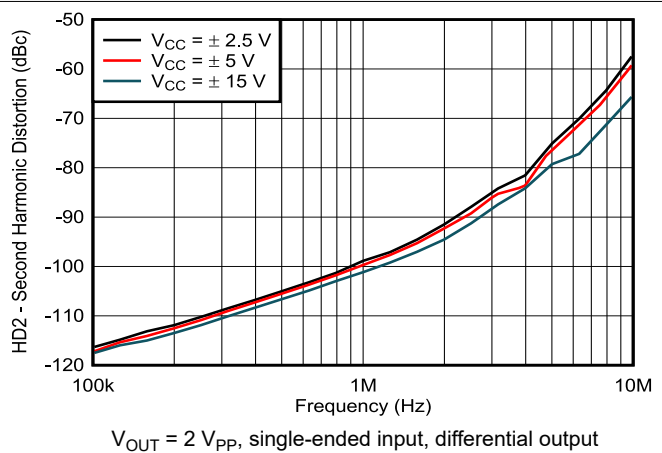


图 7-16. Second-Harmonic Distortion vs Frequency

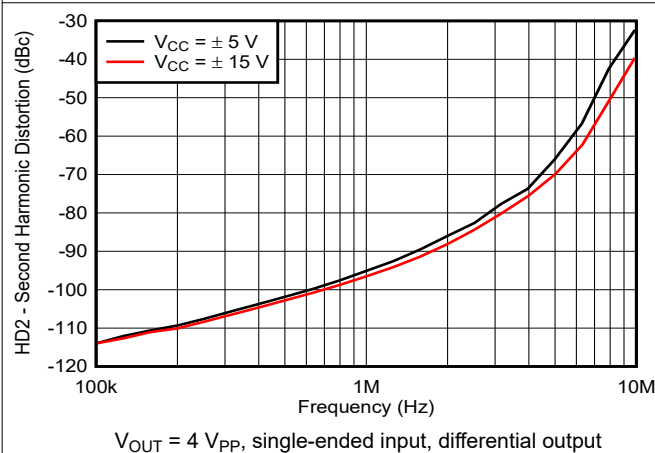


图 7-17. Second-Harmonic Distortion vs Frequency

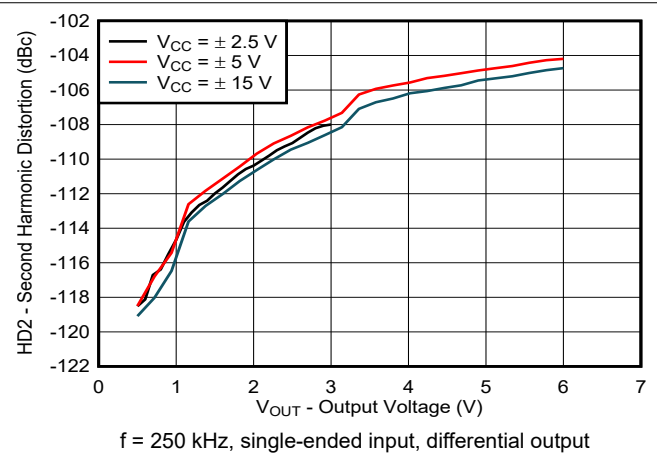
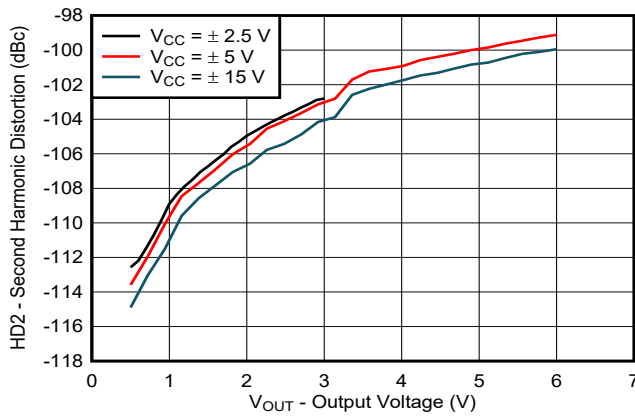


图 7-18. Second-Harmonic Distortion vs Output Voltage

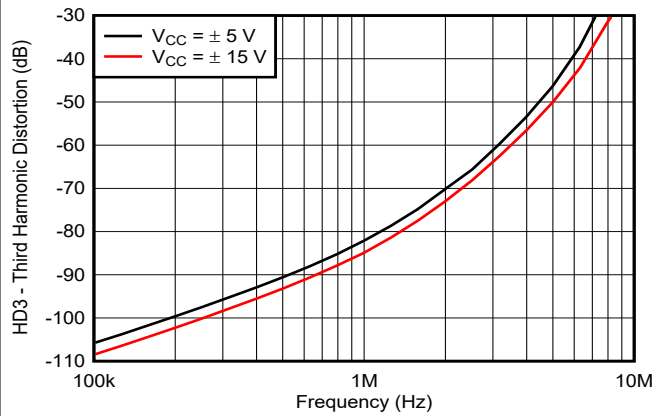
## 7.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} = \pm 5\text{ V}$ ,  $R_F = 390\ \Omega$ , gain = +1 V/V, differential input, differential output, and  $R_L = 800\ \Omega$  (unless otherwise noted)



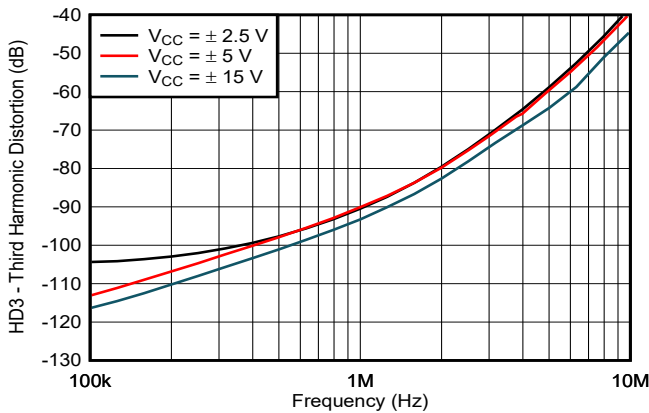
$f = 500\text{ kHz}$ , single-ended input, differential output

图 7-19. Second-Harmonic Distortion vs Output Voltage



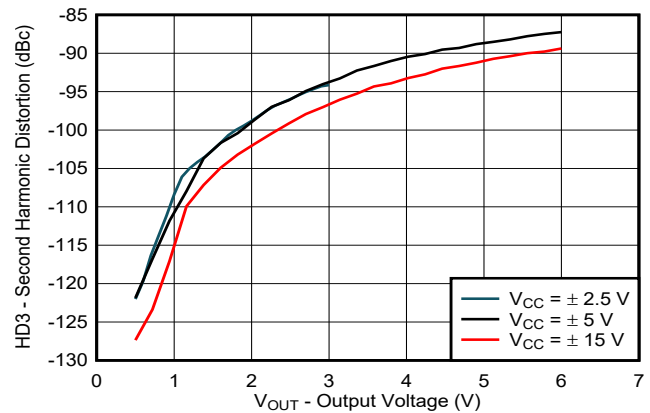
$V_{OUT} = 4\text{ V}_{PP}$ , single-ended input, differential output

图 7-20. Third-Harmonic Distortion vs Frequency



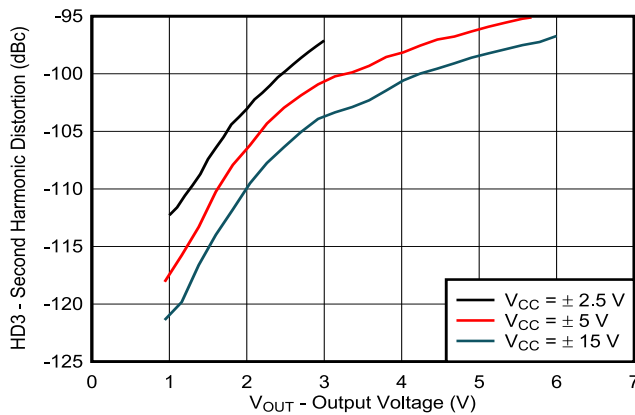
$V_{OUT} = 2\text{ V}_{PP}$ , single-ended input, differential output

图 7-21. Third-Harmonic Distortion vs Frequency



$f = 500\text{ kHz}$ , single-ended input, differential output

图 7-22. Third-Harmonic Distortion vs Output Voltage



$f = 250\text{ kHz}$ , single-ended input, differential output

图 7-23. Third-Harmonic Distortion vs Output Voltage

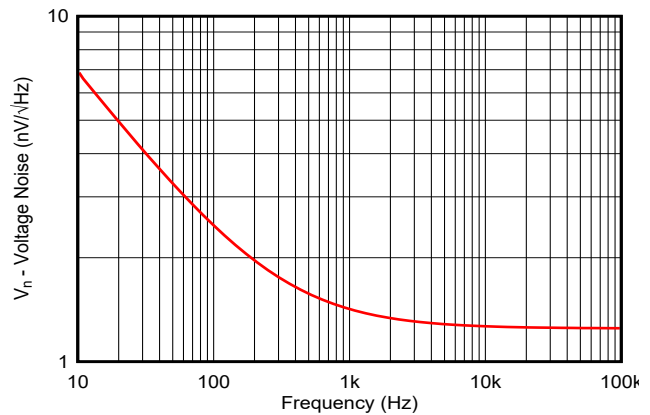


图 7-24. Voltage Noise vs Frequency

## 7.6 Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_{CC} = \pm 5\text{ V}$ ,  $R_F = 390\ \Omega$ , gain = +1 V/V, differential input, differential output, and  $R_L = 800\ \Omega$  (unless otherwise noted)

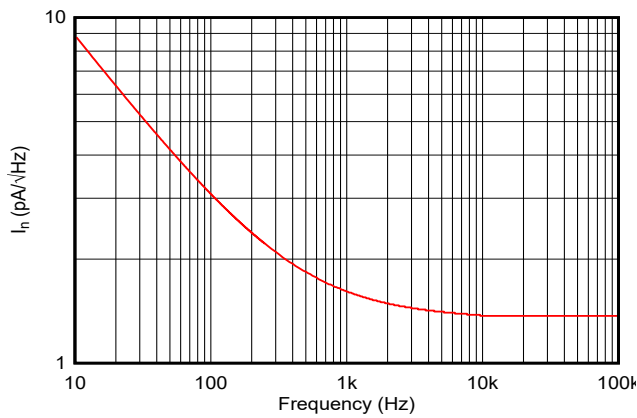


图 7-25. Current Noise vs Frequency

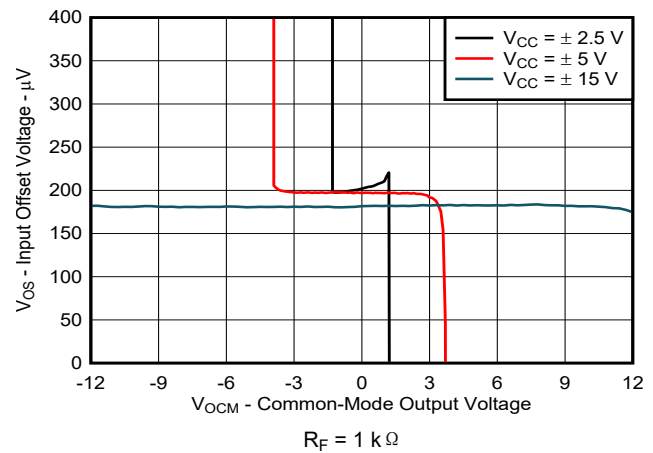


图 7-26. Input Offset Voltage vs Common-Mode Output Voltage

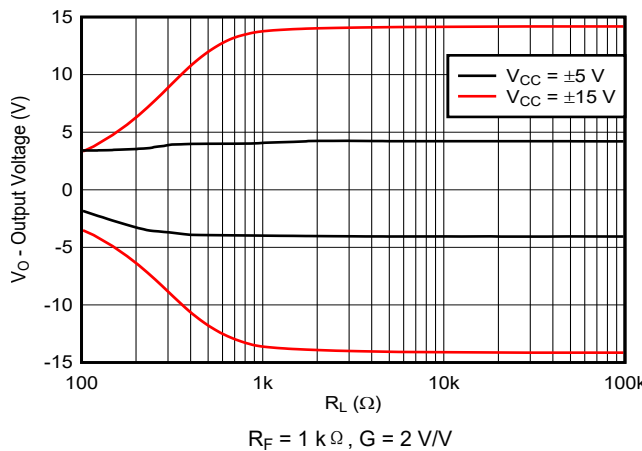


图 7-27. Output Voltage vs Differential Load Resistance

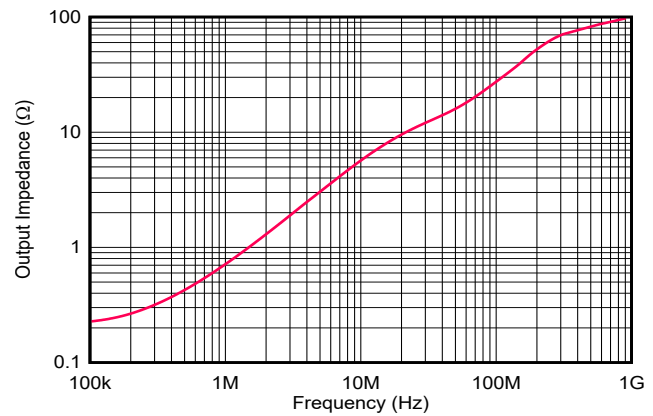


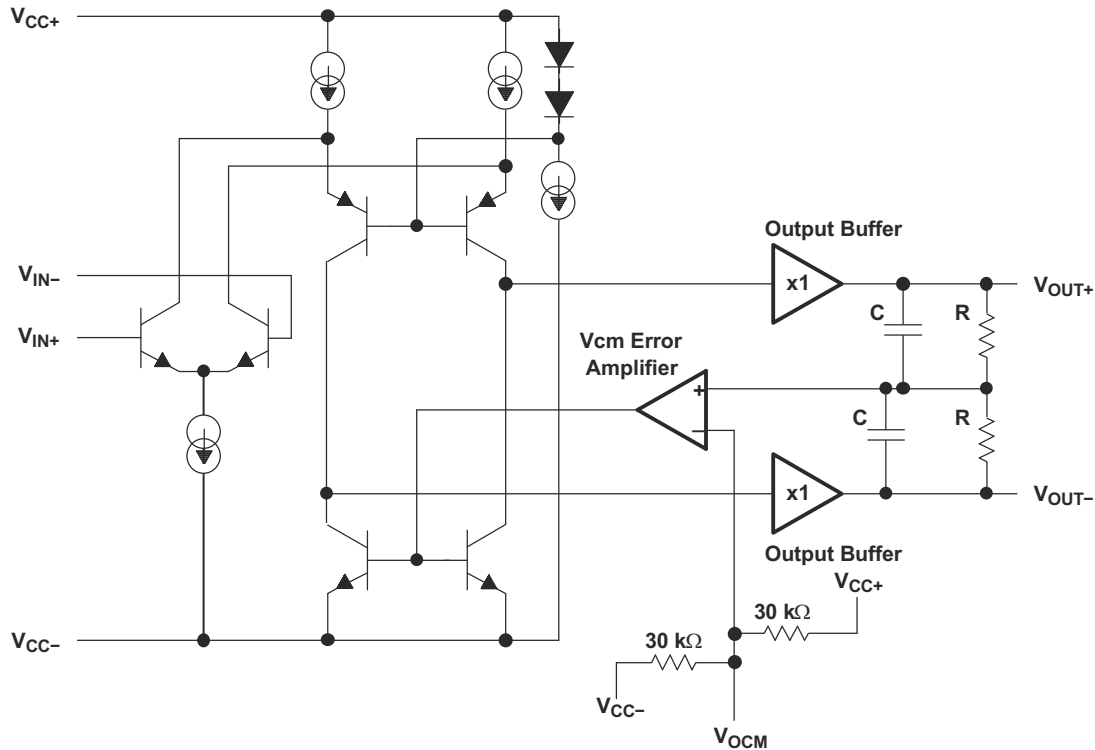
图 7-28. Output Impedance vs Frequency

## 8 Detailed Description

### 8.1 Overview

The THS413x devices are fully differential amplifiers (FDAs). Differential signal processing offers a number of performance advantages in high-speed analog signal processing systems, including immunity to external common-mode noise, suppression of even-order nonlinearities, and increased dynamic range. FDAs not only serve as the primary means of providing gain to a differential signal chain, but also provide a monolithic solution for converting single-ended signals into differential signals allowing for easy, high-performance processing. For more information on the basic theory of operation for FDAs, see the [Fully Differential Amplifiers application note](#).

### 8.2 Functional Block Diagram



### 8.3 Feature Description

图 8-1 和 图 8-2 depict the differences between the operation of the THS413x in two different modes. FDAs can work with either differential or single-ended inputs.

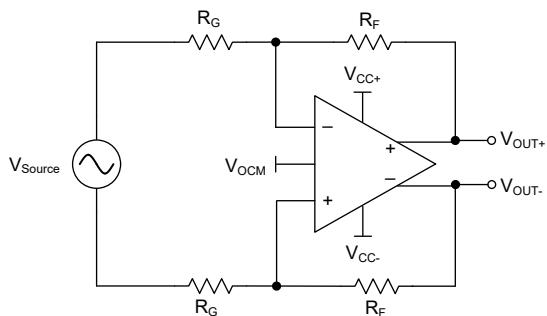


图 8-1. Amplifying Differential Input Signals

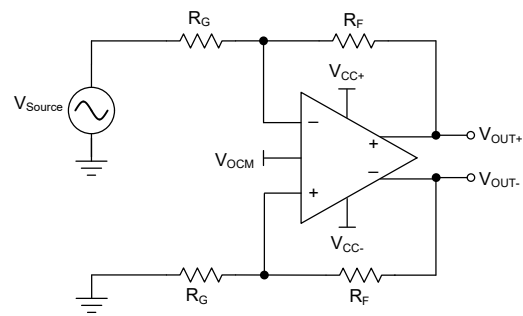


图 8-2. Amplifying Single-ended Input Signals

## 8.4 Device Functional Modes

### 8.4.1 Power-Down Mode

Power-down mode is used when power saving is required. The THS4130 power-down ( $\overline{\text{PD}}$ ) pin is an active low input. If left unconnected, an internal  $250\text{-k}\Omega$  resistor to  $V_{\text{CC}+}$  keeps the device turned on. The threshold voltage for the power-down function is approximately  $1.4\text{ V}$  greater than  $V_{\text{CC}-}$ . Therefore, if the  $\overline{\text{PD}}$  pin is  $1.4\text{ V}$  greater than  $V_{\text{CC}-}$ , then the device is active. If the  $\overline{\text{PD}}$  pin is less than  $1.4\text{ V}$  greater than  $V_{\text{CC}-}$ , then the device is off. Pull the pin to  $V_{\text{CC}-}$  to turn the device off. 图 8-3 shows the simplified version of the power-down circuit. While in power-down mode, the amplifier goes into a high-impedance state. The amplifier output impedance is typically greater than  $1\text{ M}\Omega$  in power-down mode.

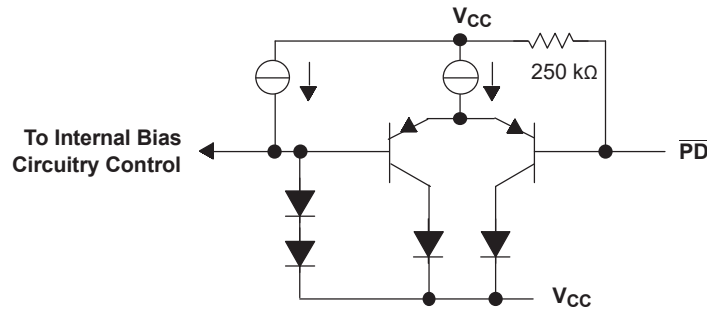


图 8-3. Simplified Power-Down Circuit

Similar to an op amp in an inverting configuration, the output impedance of an FDA is determined by the feedback network configuration. In addition, the THS4130 has an internal  $10\text{-k}\Omega$  resistor at each output that is tied to the  $V_{\text{CM}}$  error amplifier (see 节 8.2). The differential output impedance is equal to  $[(2 \times R_F + 2 \times R_G) \parallel 20\text{ k}\Omega]$ . 图 8-4 shows the closed-loop output impedance of the THS4130 when in power-down.

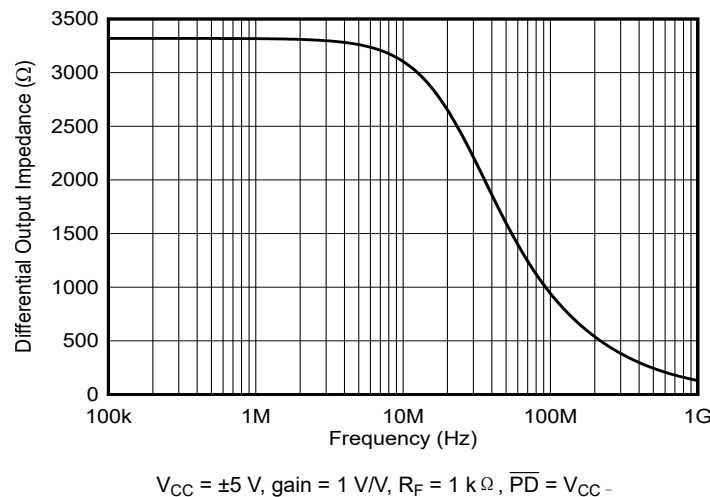


图 8-4. Output Impedance (in Power-Down) vs Frequency

## 9 Application and Implementation

### 备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

### 9.1 Application Information

#### 9.1.1 Output Common-Mode Voltage

The output common-mode voltage pin sets the dc output voltage of the THS413x. A voltage applied to the VOCM pin from a low-impedance source can be used to directly set the output common-mode voltage. If left floating, then the VOCM pin defaults to the mid-rail voltage, defined as:

$$\frac{(V_{CC+}) + (V_{CC-})}{2} \quad (1)$$

To minimize common-mode noise, connect a 0.1-μF bypass capacitor to the VOCM pin. Output common-mode voltage causes additional current to flow in the feedback resistor network. This current is supplied by the output stage of the amplifier; therefore, additional power dissipation is created. For commonly-used feedback resistance values, this current is easily supplied by the amplifier. The additional internal power dissipation created by this current can be significant in some applications and can dictate the use of the HVSSOP package to effectively control self-heating.

##### 9.1.1.1 Resistor Matching

Resistor matching is important in FDAs to maintain good output balance. An ideal differential output signal implies the two outputs of the FDA should be exactly equal in amplitude and shifted 180° in phase. Any imbalance in amplitude or phase between the two output signals results in an undesirable common-mode signal at the output. The output balance error is a measure of how well the outputs are balanced and is defined as the ratio of the output common-mode voltage to the output differential signal.

$$\text{Output Balance Error} = \frac{\left( \frac{V_{OUT+} - V_{OUT-}}{2} \right)}{V_{OUT+} - V_{OUT-}} \quad (2)$$

At low frequencies, resistor mismatch is the primary contributor to output balance errors. Additionally CMRR, PSRR, and HD2 performance diminish if resistor mismatch occurs. Therefore, to optimize performance, use 1% tolerance resistors or better. 表 9-1 provides the recommended resistor values to use for a particular gain.

**表 9-1. Recommended Resistor Values**

| GAIN (V/V) | R <sub>G</sub> (Ω) | R <sub>F</sub> (Ω) |
|------------|--------------------|--------------------|
| 1          | 390                | 390                |
| 2          | 374                | 750                |
| 5          | 402                | 2010               |
| 10         | 402                | 4020               |

### 9.1.2 Driving a Capacitive Load

Driving capacitive loads with high-performance amplifiers is not a problem as long as certain precautions are taken. The THS413x have been internally compensated to maximize bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output decreases the device phase margin leading to high-frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, place a resistor in series with the output of the amplifier, as shown in 图 9-1. A minimum value of 20  $\Omega$  works well for most applications. For example, in 50- $\Omega$  transmission systems, setting the series resistor value to 50  $\Omega$  both isolates any capacitance loading and provides the proper line impedance matching at the source end.

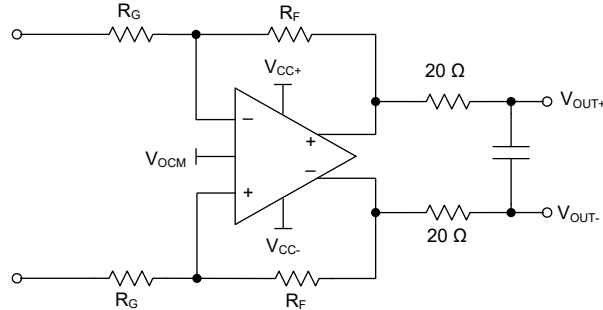


图 9-1. Driving a Capacitive Load

### 9.1.3 Data Converters

Driving data converters are one of the most popular applications for fully-differential amplifiers. 图 9-2 shows a typical configuration of an FDA attached to a differential analog-to-digital converter (ADC).

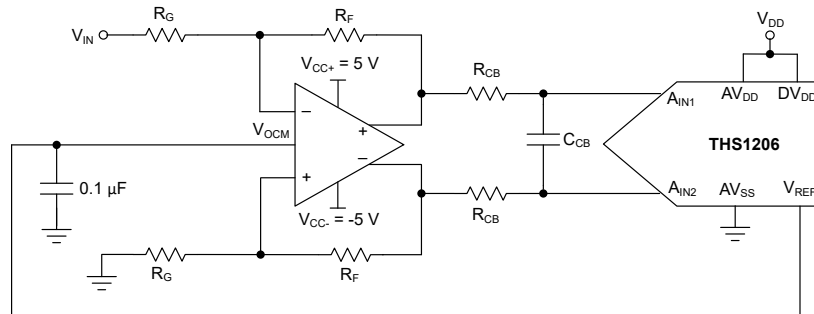


图 9-2. Fully-Differential Amplifier Attached to a Differential ADC

FDAs can operate with a single supply.  $V_{OCM}$  defaults to the mid-rail voltage,  $V_{CC}/2$ . The differential output can be fed into a data converter. This method eliminates the use of a transformer in the circuit. If the ADC has a reference voltage output ( $V_{ref}$ ), then connect  $V_{ref}$  directly to the  $V_{OCM}$  of the amplifier using a bypass capacitor to reduce broadband common-mode noise.

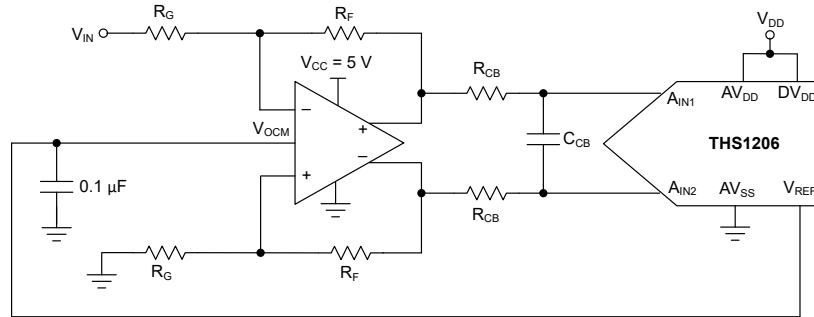


图 9-3. Fully-Differential Amplifier Using a Single Supply

### 9.1.4 Single-Supply Applications

For proper operation, the input common-mode voltage to the input terminal of the amplifier must not exceed the common-mode input voltage range. However, some single-supply applications can require the input voltage to exceed the common-mode input voltage range. In such cases, to bring the common-mode input voltage within the specifications of the amplifier, the circuit configuration of 图 9-4 is suggested.

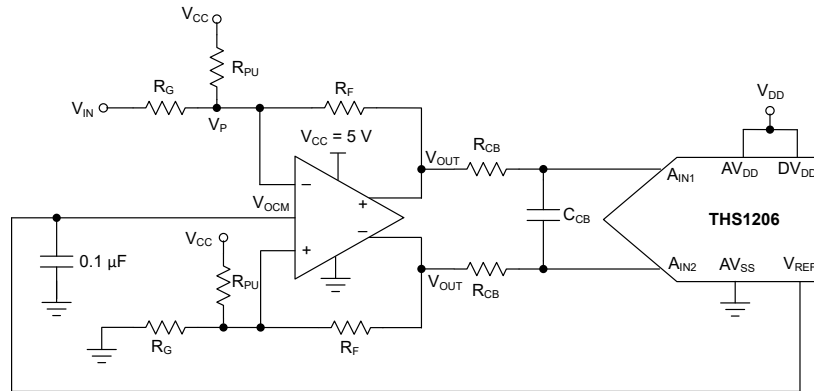


图 9-4. Circuit With Improved Common-Mode Input Voltage

方程式 3 is used to calculate  $R_{PU}$ :

$$R_{PU} = \frac{V_P - V_{CC}}{(V_{IN} - V_P) \frac{1}{R_G} + (V_{OUT} - V_P) \frac{1}{R_F}} \quad (3)$$



## 9.2 Typical Application

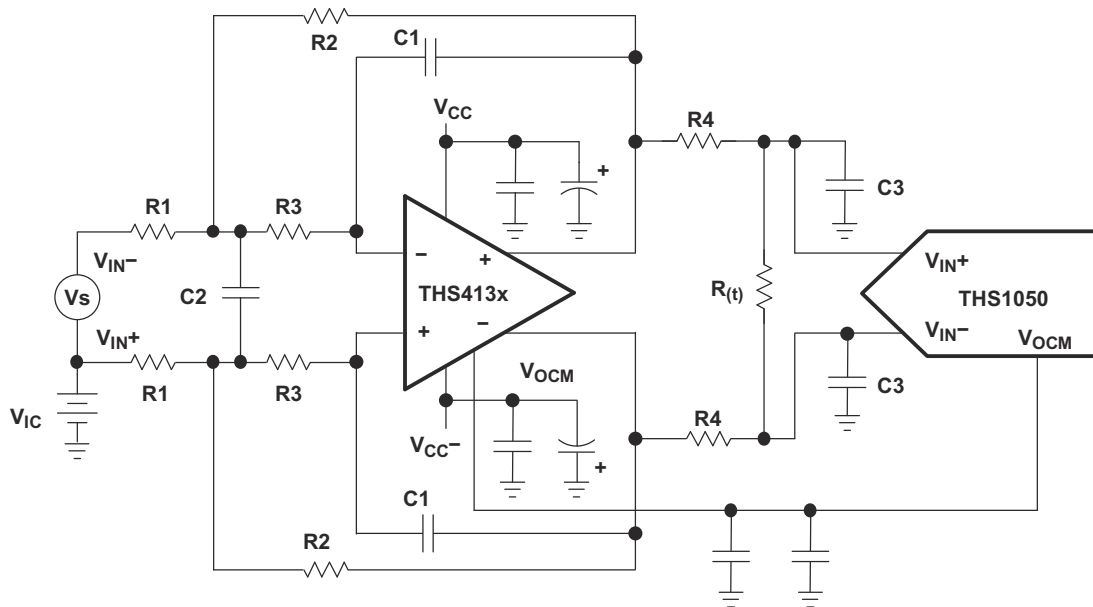


图 9-5. Antialias Filtering

For signal conditioning in ADC applications, make sure to limit the input frequency to the ADC. Low-pass filters can prevent the aliasing of the high-frequency noise with the frequency of operation. This design example shows a method by which the noise can be filtered in the THS413x. 图 9-5 shows the design example for the THS413x in active low-pass filter topology driving an ADC.

### 9.2.1 Design Requirements

表 9-2 shows example design parameters and values for the typical application design example in 图 9-5.

表 9-2. Design Parameters

| DESIGN PARAMETERS  | VALUE                                                 |
|--------------------|-------------------------------------------------------|
| Supply voltage     | ±2.5 V to ±15 V                                       |
| Amplifier topology | Voltage feedback                                      |
| Output control     | DC-coupled with output common-mode control capability |
| Filter requirement | 500-kHz, multiple-feedback low-pass filter            |

### 9.2.2 Detailed Design Procedure

图 9-5 shows a multiple-feedback (MFB) low-pass filter. The transfer function for this filter circuit is:

$$H_d(f) = \left[ \frac{K}{-\left[\frac{f}{FSF \times f_c}\right]^2 + \frac{1}{Q} \frac{jf}{FSF \times f_c} + 1} \right] \times \left[ \frac{\frac{R_t}{2R_4 + R_t}}{1 + \frac{j2\pi f R_4 R_t C_3}{2R_4 + R_t}} \right]$$

$$\text{where } K = \frac{R_2}{R_1}, FSF \times f_c = \frac{1}{2\pi\sqrt{2 \times R_2 R_3 C_1 C_2}}, \text{ and } Q = \frac{\sqrt{2 \times R_2 R_3 C_1 C_2}}{R_3 C_1 + R_2 C_1 + K R_3 C_1} \quad (4)$$

K sets the pass-band gain,  $f_c$  is the cutoff frequency for the filter, FSF is a frequency scaling factor, and Q is the quality factor.

$$FSF = \sqrt{Re^2 + |Im|^2} \text{ and } Q = \frac{\sqrt{Re^2 + |Im|^2}}{2Re} \quad (5)$$

where Re is the real part and Im is the imaginary part of the complex pole pair. Setting  $R2 = R$ ,  $R3 = mR$ ,  $C1 = C$ , and  $C2 = nC$  results in:

$$FSF \times fc = \frac{1}{2\pi Rc\sqrt{2 \times mn}} \text{ and } Q = \frac{\sqrt{2 \times mn}}{1 + m(1 + K)} \quad (6)$$

Start by determining the ratios, m and n, required for the gain and Q of the filter type being designed, then select C and calculate R for the desired  $fc$ .

### 9.2.3 Application Curve

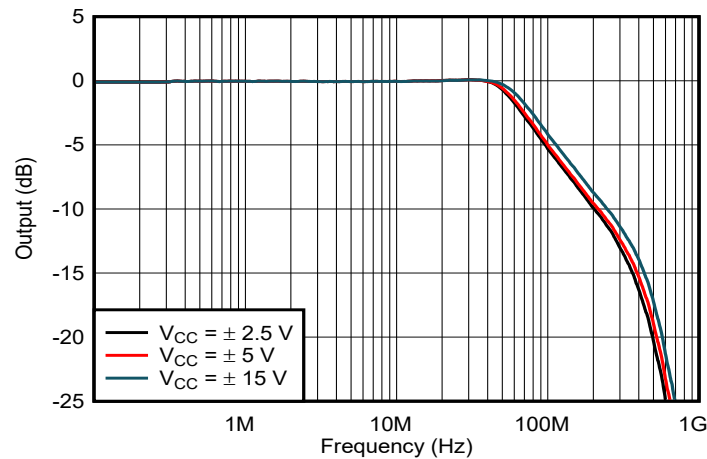


图 9-6. Large-Signal Frequency Response

## 9.3 Power Supply Recommendations

The THS413x devices are designed to operate on power supplies ranging from  $\pm 2.5$  V to  $\pm 15$  V (single-ended supplies of 5 V to 30 V). Use a power-supply accuracy of 5% or better. When operated on a board with high-speed digital signals, make sure to provide isolation between digital signal noise and the analog input pins. The THS413x are connected to power supplies through pin 3 ( $V_{CC+}$ ) and pin 6 ( $V_{CC-}$ ). Decouple each supply pin to GND as close to the device as possible with a low-inductance, surface-mount ceramic capacitor of approximately 10 nF. When vias are used to connect the bypass capacitors to a ground plane, configure the vias for minimal parasitic inductance. One method of reducing via inductance is to use multiple vias. For broadband systems, two capacitors per supply pin are advised.

To avoid undesirable signal transients, do not power on the THS413x with large inputs signals present. Careful planning of system power on sequencing is especially important to avoid damage to ADC inputs when an ADC is used in the application.

## 9.4 Layout

### 9.4.1 Layout Guidelines

To achieve the levels of high-frequency performance of the THS413x devices, follow proper printed-circuit board (PCB) high-frequency design techniques. Following is a general set of guidelines. In addition, a [THS413x evaluation board](#) is available to use as a guide for layout or for evaluating device performance.

- Ground planes—Use a ground plane on the board to provide all components with a low inductive ground connection. However, in the areas of the amplifier inputs and output, the ground plane can be removed to minimize the stray capacitance.
- Proper power-supply decoupling—use a 6.8- $\mu$ F tantalum capacitor in parallel with a 0.1- $\mu$ F ceramic capacitor on each supply pin. Sharing the tantalum among several amplifiers is possible depending on the application; however, always use a 0.1- $\mu$ F ceramic capacitor on the supply pin of every amplifier. In addition, place the 0.1- $\mu$ F capacitor as close as possible to the supply pin. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. Strive for distances of less than 0.1 inches between the device power pin and the ceramic capacitors.
- Short trace runs or compact part placements—to optimize high-frequency performance, minimize stray series inductance. The best method is to make the circuit layout as compact as possible, thereby minimizing the length of all trace runs. Pay particular attention to the inputs of the amplifier; keep the length as short as possible. This short length helps minimize stray capacitance at the input of the amplifier.

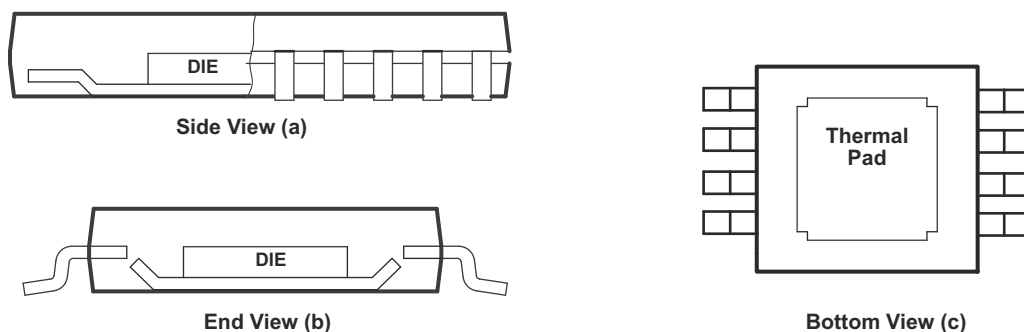
#### 9.4.1.1 PowerPAD™ Integrated Circuit Package Design Considerations

The THS413x is available in a thermally-enhanced DGN package, which is a member of the PowerPAD™ integrated circuit package family. This package is constructed using a downset leadframe upon which the die is mounted (see [图 9-7 a](#) and [图 9-7 b](#)). This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package (see [图 9-7 c](#)). Because this thermal pad has direct thermal contact with the die, excellent thermal performance can be achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat dissipating device.

The PowerPAD package represents a breakthrough in combining the small area and ease of assembly of the surface mount with the previously awkward mechanical methods of using a heat sink.

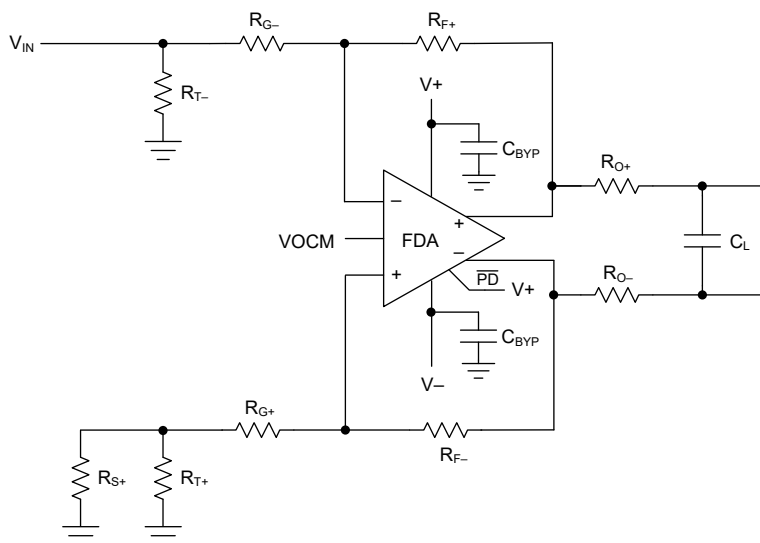
More complete details of the PowerPAD installation process and thermal management techniques can be found in [PowerPAD Thermally-Enhanced Package application report](#). This document can be found on the TI website at [www.ti.com](http://www.ti.com) by searching for the keyword PowerPAD. The document can also be ordered through your local TI sales office; refer to SLMA002 when ordering.



Note: The thermal pad (PowerPAD) is electrically isolated from all other pins and can be connected to any potential from  $V_{CC-}$  to  $V_{CC+}$ . Typically, the thermal pad is connected to the ground plane because this plane tends to physically be the largest and is able to dissipate the most amount of heat.

### 图 9-7. Views of Thermally-Enhanced DGN Package

### 9.4.2 Layout Example



**图 9-8. Representative Schematic for Layout**

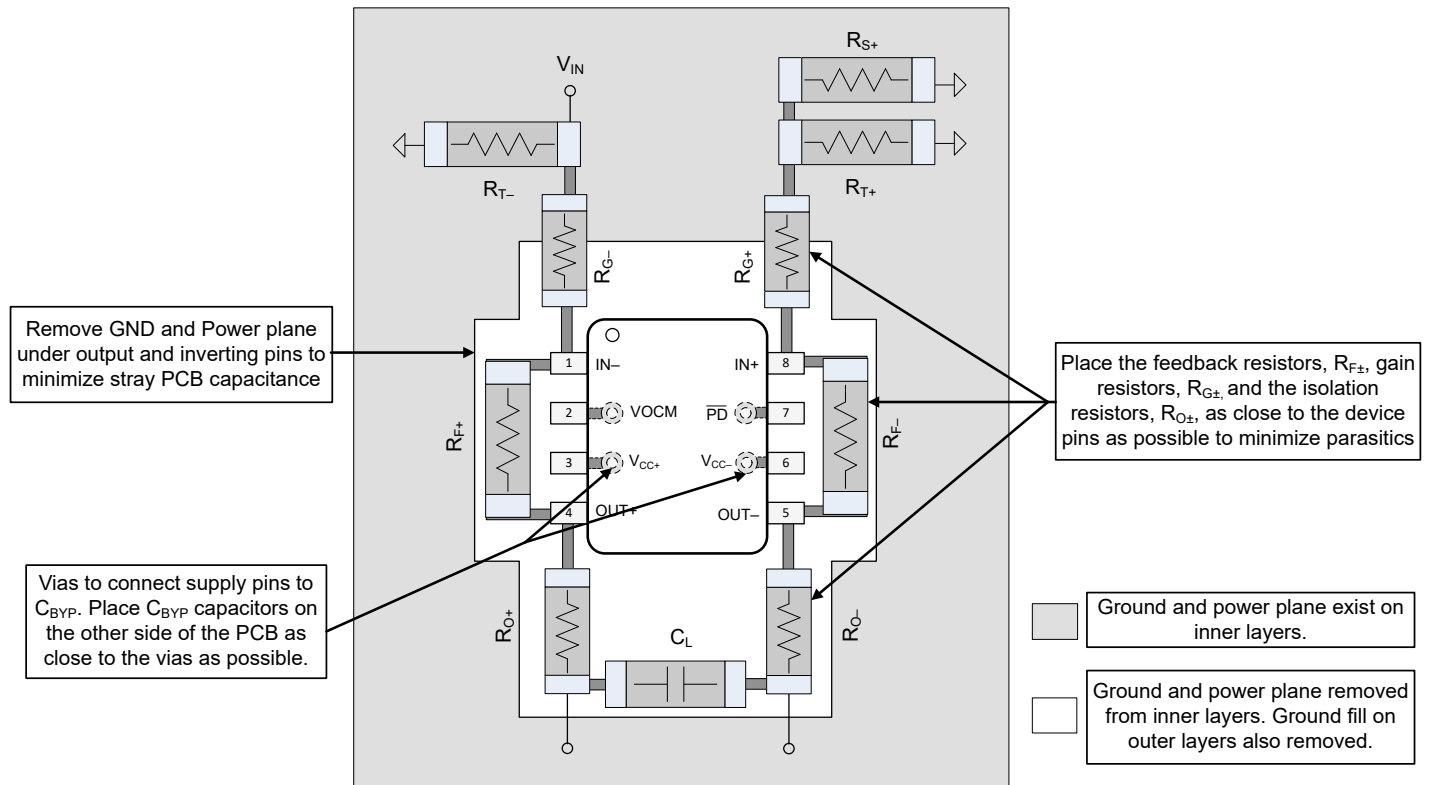


图 9-9. Layout Recommendations

## 10 Device and Documentation Support

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Design Guide for 2.3 nV/√Hz, Differential, Time Gain Control \(TGC\) DAC Reference Design for Ultrasound design guide](#)
- Texas Instruments, [EVM User's Guide for High-Speed Fully-Differential Amplifier user's guide](#)
- Texas Instruments, [Fully Differential Amplifiers application note](#)
- Texas Instruments, [Maximizing Signal Chain Distortion Performance Using High Speed Amplifiers application note](#)
- Texas Instruments, [PowerPAD Thermally-Enhanced Package application report](#)
- Texas Instruments, [PowerPAD™ Made Easy application report](#)
- Texas Instruments, [TI Precision Labs - Fully Differential Amplifiers video series](#)

### 10.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](http://ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 10.3 支持资源

**TI E2E™ 支持论坛** 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

### 10.4 Trademarks

PowerPAD™ and TI E2E™ are trademarks of Texas Instruments.

所有商标均为其各自所有者的财产。

### 10.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

### 10.6 术语表

**TI 术语表** 本术语表列出并解释了术语、首字母缩略词和定义。

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

| Orderable part number            | Status<br>(1) | Material type<br>(2) | Package   Pins   | Package qty   Carrier | RoHS<br>(3) | Lead finish/<br>Ball material<br>(4) | MSL rating/<br>Peak reflow<br>(5) | Op temp (°C) | Part marking<br>(6) |
|----------------------------------|---------------|----------------------|------------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| <a href="#">THS4130CD</a>        | Obsolete      | Production           | SOIC (D)   8     | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | 4130C               |
| <a href="#">THS4130CDGN</a>      | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | AOB                 |
| <a href="#">THS4130CDGNR</a>     | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | AOB                 |
| <a href="#">THS4130IDGKR</a>     | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASO                 |
| <a href="#">THS4130IDGKR.B</a>   | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASO                 |
| <a href="#">THS4130IDGN</a>      | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | -40 to 85    | AOC                 |
| <a href="#">THS4130IDGNR</a>     | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | (4130, AOC)         |
| <a href="#">THS4130IDGNR.B</a>   | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | (4130, AOC)         |
| <a href="#">THS4130IDGNRG4</a>   | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | 4130                |
| <a href="#">THS4130IDGNRG4.B</a> | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | 4130                |
| <a href="#">THS4130IDR</a>       | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4130I               |
| <a href="#">THS4130IDR.B</a>     | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4130I               |
| <a href="#">THS4130IDRG4</a>     | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4130I               |
| <a href="#">THS4130IDRG4.A</a>   | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4130I               |
| <a href="#">THS4130IDRG4.B</a>   | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4130I               |
| <a href="#">THS4131CD</a>        | Obsolete      | Production           | SOIC (D)   8     | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | 4131C               |
| <a href="#">THS4131CDGN</a>      | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | AOD                 |
| <a href="#">THS4131CDGNR</a>     | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | AOD                 |
| <a href="#">THS4131CDR</a>       | Obsolete      | Production           | SOIC (D)   8     | -                     | -           | Call TI                              | Call TI                           | 0 to 70      | 4131C               |
| <a href="#">THS4131ID</a>        | Obsolete      | Production           | SOIC (D)   8     | -                     | -           | Call TI                              | Call TI                           | -40 to 85    | 4131I               |
| <a href="#">THS4131IDGKR</a>     | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASP                 |
| <a href="#">THS4131IDGKR.B</a>   | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASP                 |
| <a href="#">THS4131IDGKRG4</a>   | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASP                 |
| <a href="#">THS4131IDGKRG4.A</a> | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASP                 |
| <a href="#">THS4131IDGKRG4.B</a> | Active        | Production           | VSSOP (DGK)   8  | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | ASP                 |
| <a href="#">THS4131IDGN</a>      | Obsolete      | Production           | HVSSOP (DGN)   8 | -                     | -           | Call TI                              | Call TI                           | -40 to 85    | AOE                 |
| <a href="#">THS4131IDGNR</a>     | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | (4131, AOE)         |
| <a href="#">THS4131IDGNR.B</a>   | Active        | Production           | HVSSOP (DGN)   8 | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-2-260C-1 YEAR               | -40 to 85    | (4131, AOE)         |
| <a href="#">THS4131IDR</a>       | Active        | Production           | SOIC (D)   8     | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4131I               |

| Orderable part number | Status<br>(1) | Material type<br>(2) | Package   Pins | Package qty   Carrier | RoHS<br>(3) | Lead finish/<br>Ball material<br>(4) | MSL rating/<br>Peak reflow<br>(5) | Op temp (°C) | Part marking<br>(6) |
|-----------------------|---------------|----------------------|----------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| THS4131IDR.B          | Active        | Production           | SOIC (D)   8   | 2500   LARGE T&R      | Yes         | NIPDAU                               | Level-1-260C-UNLIM                | -40 to 85    | 4131I               |

- <sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).
- <sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- <sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.
- <sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- <sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- <sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



## TAPE AND REEL INFORMATION



\*All dimensions are nominal

| Device         | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|----------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| THS4130IDGKR   | VSSOP        | DGK             | 8    | 2500 | 330.0              | 12.4               | 5.25    | 3.35    | 1.25    | 8.0     | 12.0   | Q1            |
| THS4130IDGNR   | HVSSOP       | DGN             | 8    | 2500 | 330.0              | 12.4               | 5.3     | 3.4     | 1.4     | 8.0     | 12.0   | Q1            |
| THS4130IDGNRG4 | HVSSOP       | DGN             | 8    | 2500 | 330.0              | 12.4               | 5.3     | 3.4     | 1.4     | 8.0     | 12.0   | Q1            |
| THS4130IDR     | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| THS4130IDRG4   | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| THS4131IDGKR   | VSSOP        | DGK             | 8    | 2500 | 330.0              | 12.4               | 5.25    | 3.35    | 1.25    | 8.0     | 12.0   | Q1            |
| THS4131IDGKRG4 | VSSOP        | DGK             | 8    | 2500 | 330.0              | 12.4               | 5.25    | 3.35    | 1.25    | 8.0     | 12.0   | Q1            |
| THS4131IDGNR   | HVSSOP       | DGN             | 8    | 2500 | 330.0              | 12.4               | 5.3     | 3.4     | 1.4     | 8.0     | 12.0   | Q1            |
| THS4131IDR     | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

| Device         | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| THS4130IDGKR   | VSSOP        | DGK             | 8    | 2500 | 366.0       | 364.0      | 50.0        |
| THS4130IDGNR   | HVSSOP       | DGN             | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| THS4130IDGNRG4 | HVSSOP       | DGN             | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| THS4130IDR     | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| THS4130IDRG4   | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| THS4131IDGKR   | VSSOP        | DGK             | 8    | 2500 | 366.0       | 364.0      | 50.0        |
| THS4131IDGKRG4 | VSSOP        | DGK             | 8    | 2500 | 366.0       | 364.0      | 50.0        |
| THS4131IDGNR   | HVSSOP       | DGN             | 8    | 2500 | 353.0       | 353.0      | 32.0        |
| THS4131IDR     | SOIC         | D               | 8    | 2500 | 353.0       | 353.0      | 32.0        |



## VSSOP - 1.1 mm max height

[illegible]

PowerPAD is a trademark of Texas Instruments.

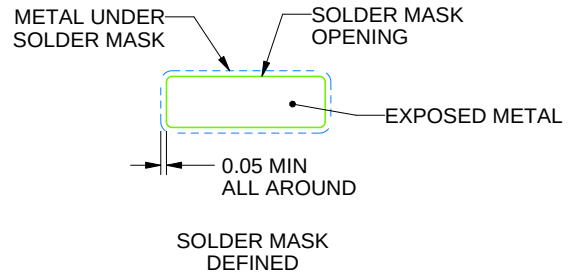
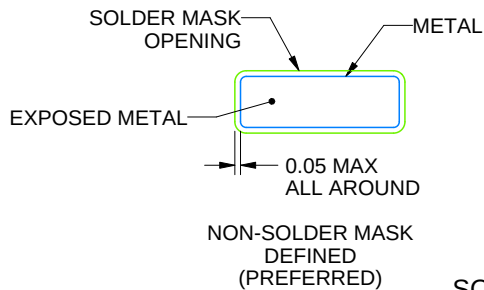
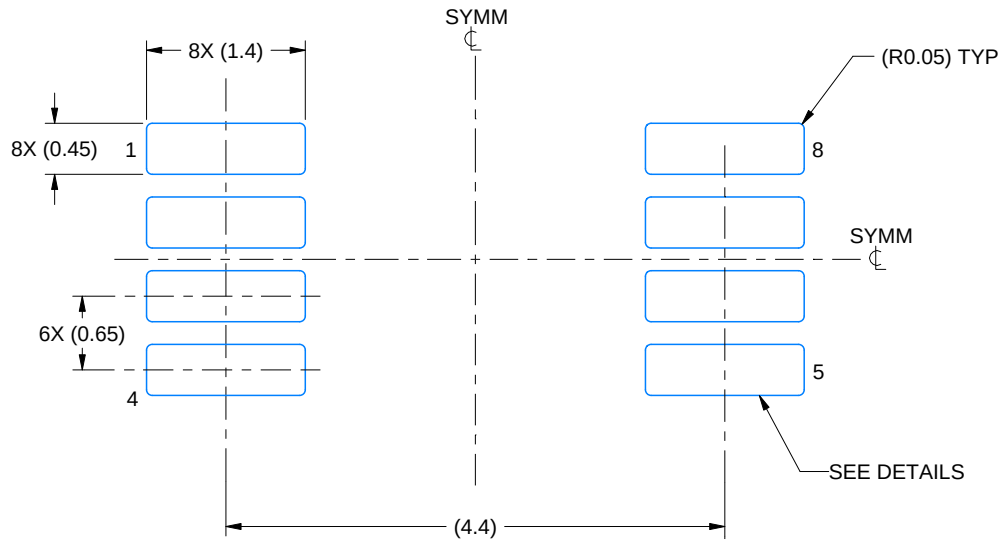
- 
- TEXAS  
INSTRUMENTS**  
www.ti.com

# EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

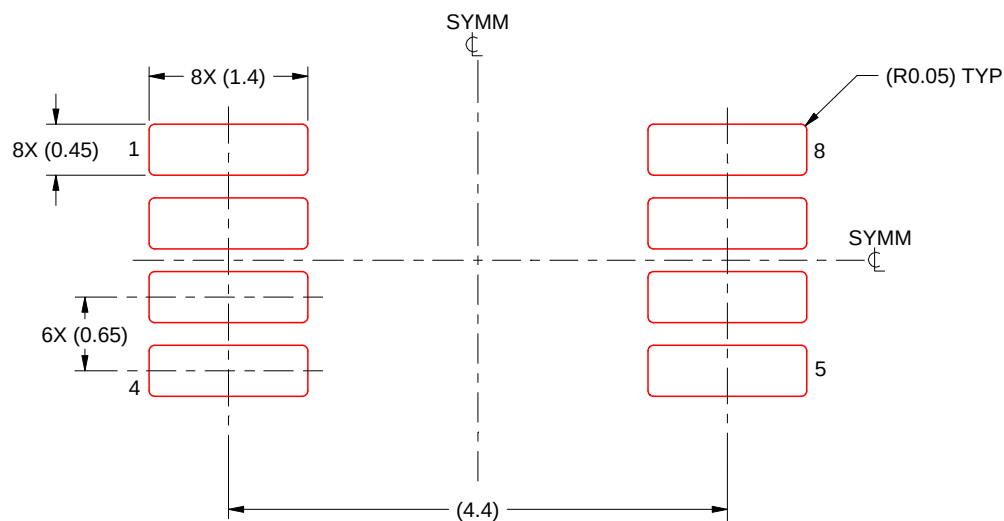
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

## EXAMPLE STENCIL DESIGN

DGK0008A

<sup>TM</sup> VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

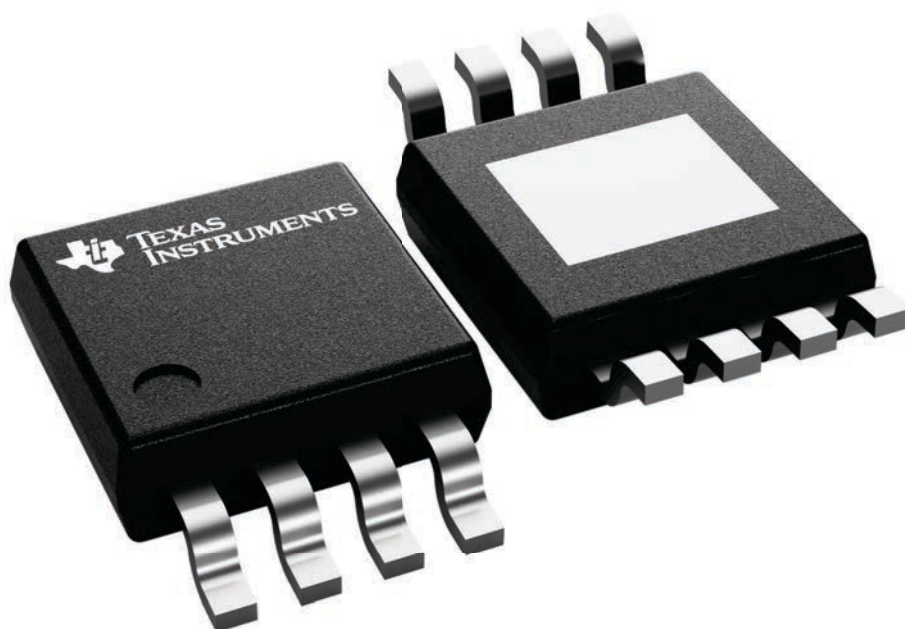
**DGN 8**

**PowerPAD™ HVSSOP - 1.1 mm max height**

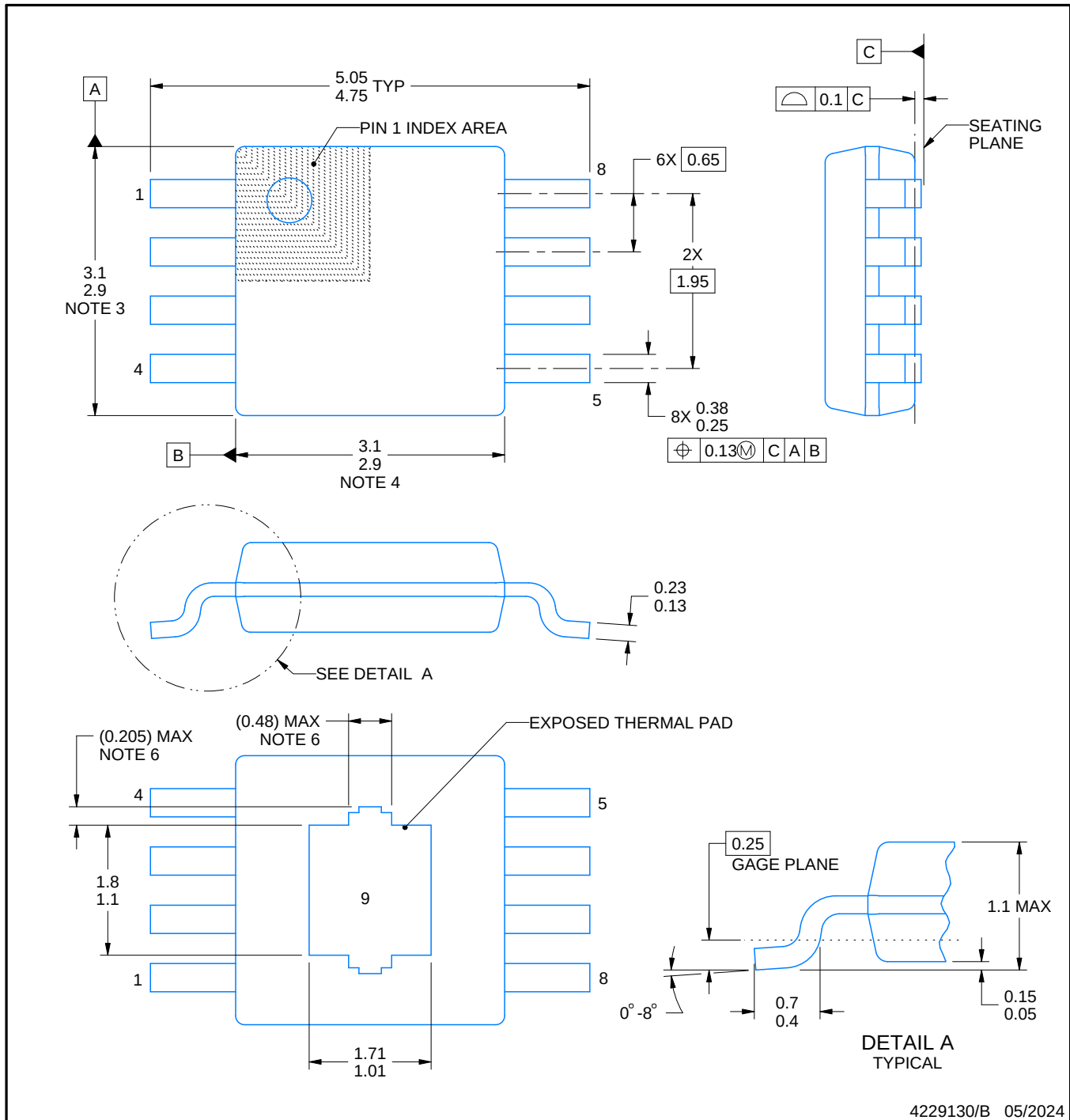
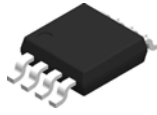
3 x 3, 0.65 mm pitch

SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4225482/B



4229130/B 05/2024

## NOTES:

PowerPAD is a trademark of Texas Instruments.

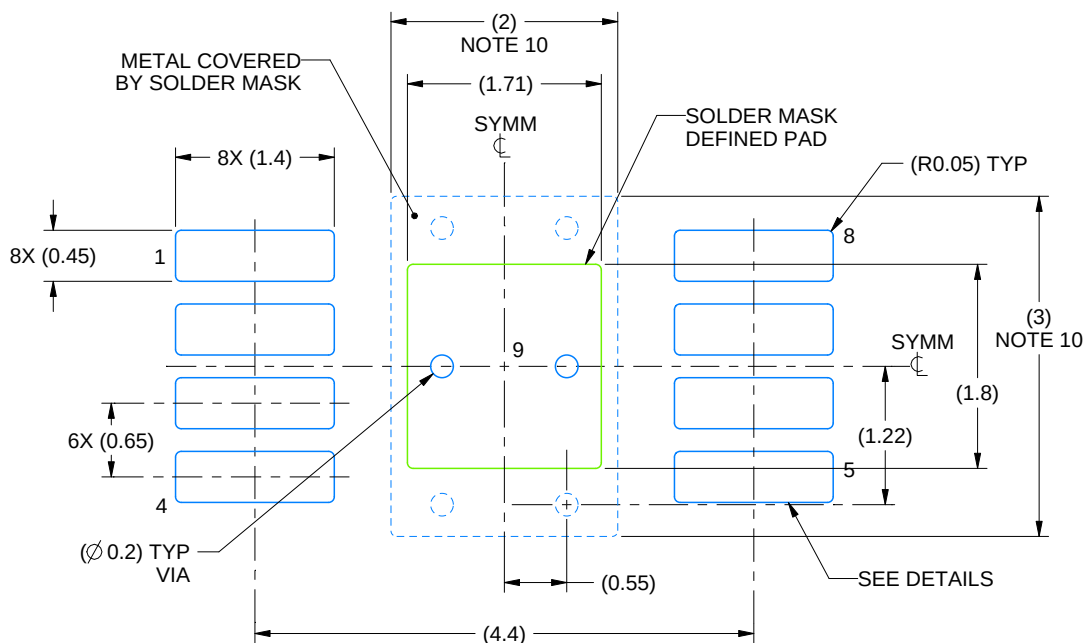
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.
6. Features may differ or may not be present.

# EXAMPLE BOARD LAYOUT

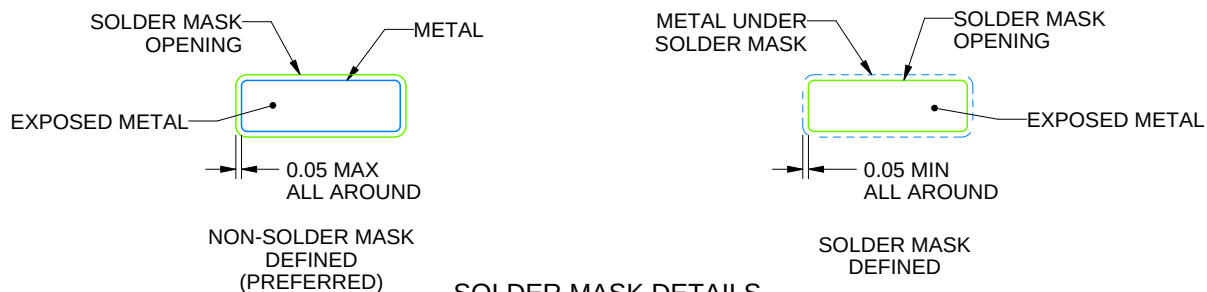
DGN0008H

PowerPAD™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 15X



SOLDER MASK DETAILS

4229130/B 05/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
9. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
10. Size of metal pad may vary due to creepage requirement.

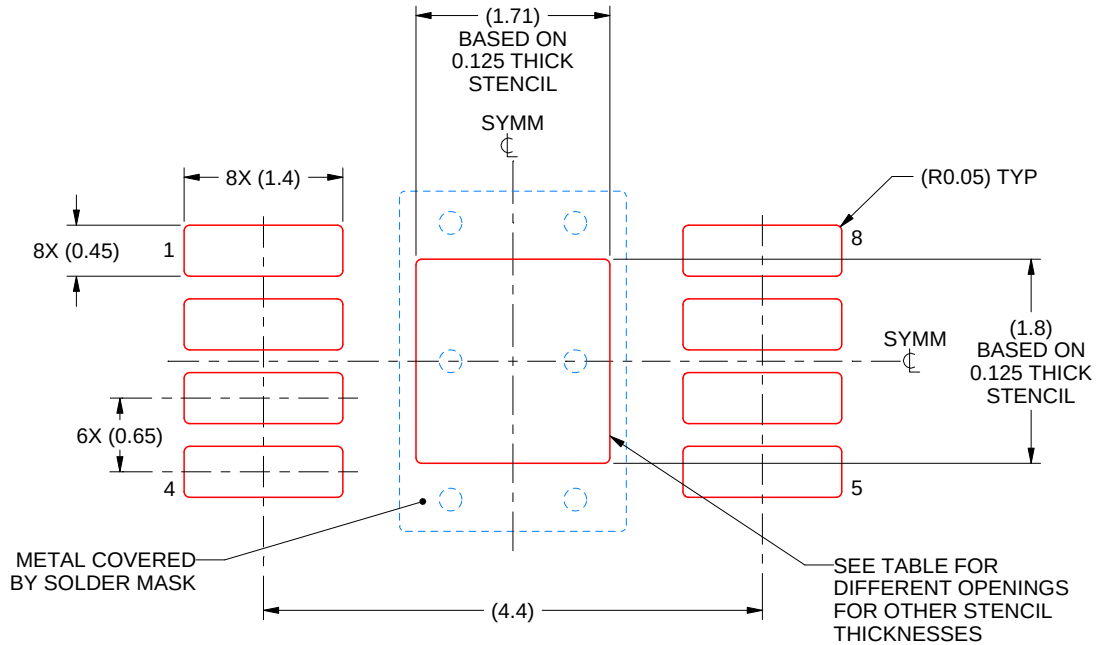


# EXAMPLE STENCIL DESIGN

DGN0008H

PowerPAD™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



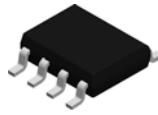
**SOLDER PASTE EXAMPLE**  
EXPOSED PAD 9:  
100% PRINTED SOLDER COVERAGE BY AREA  
SCALE: 15X

| STENCIL THICKNESS | SOLDER STENCIL OPENING |
|-------------------|------------------------|
| 0.1               | 1.91 X 2.01            |
| 0.125             | 1.71 X 1.80 (SHOWN)    |
| 0.15              | 1.56 X 1.64            |
| 0.175             | 1.45 X 1.52            |

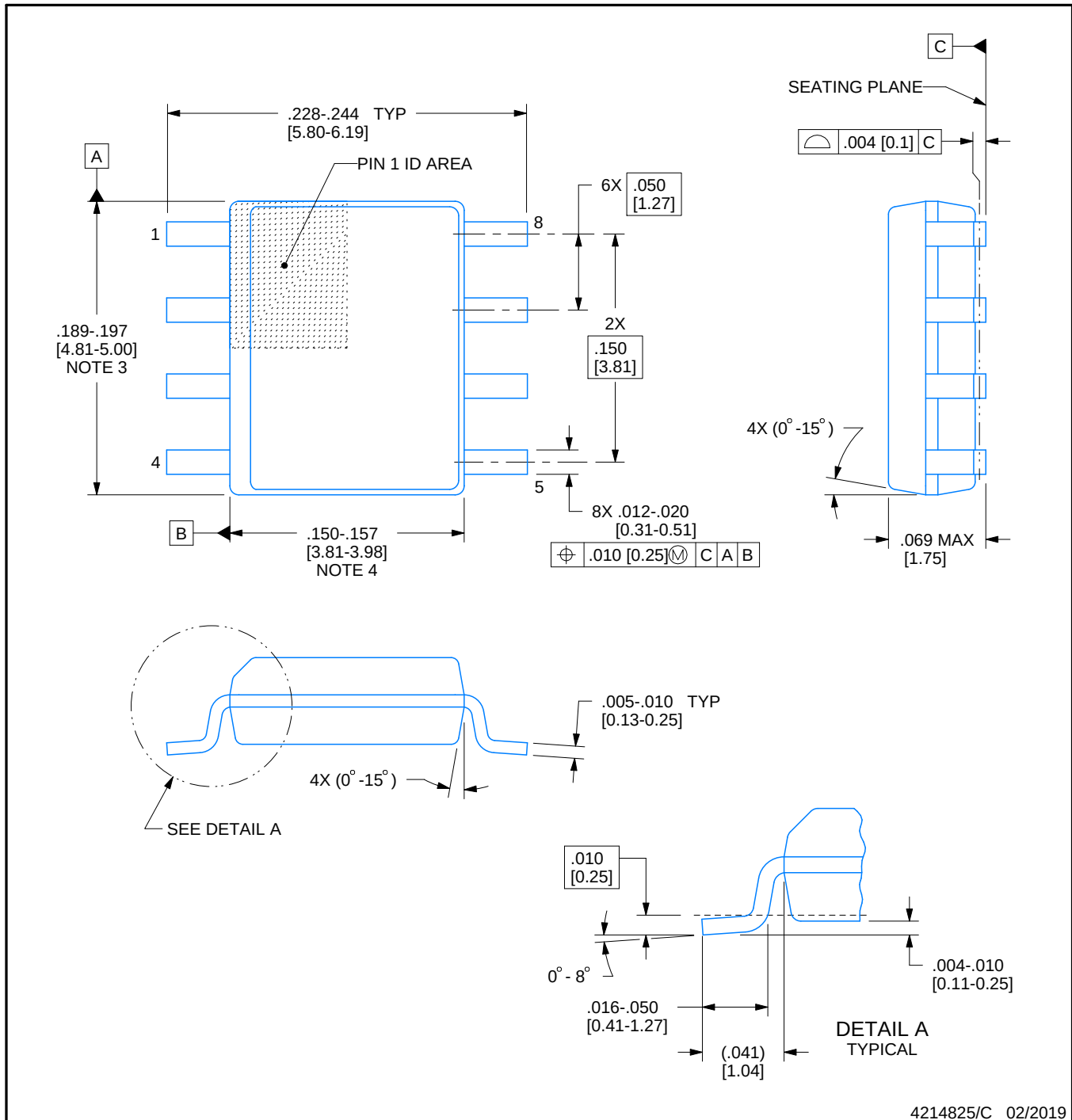
4229130/B 05/2024

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

**D0008A****PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

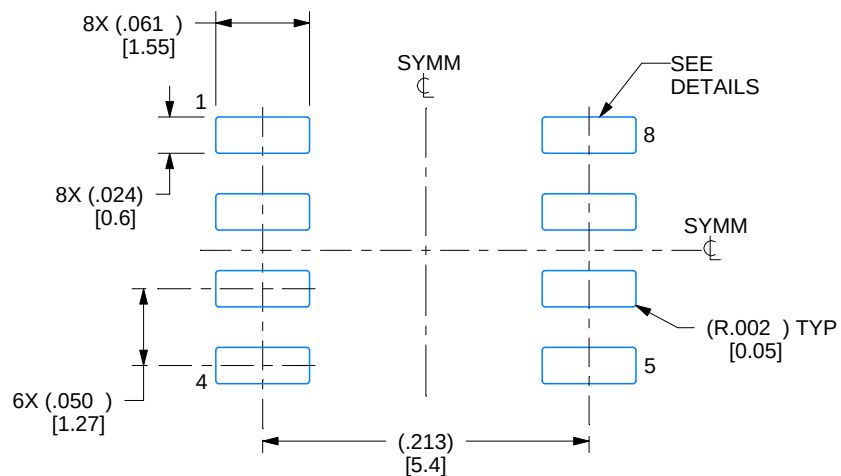
**NOTES:**

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

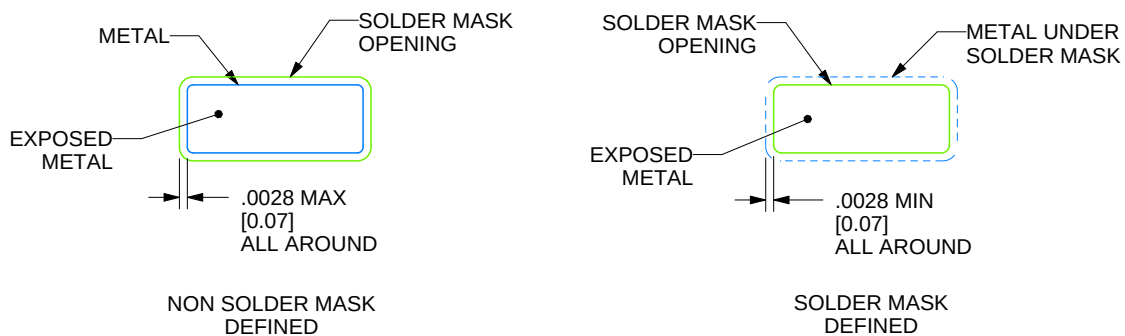
**D0008A**

### SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



## SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

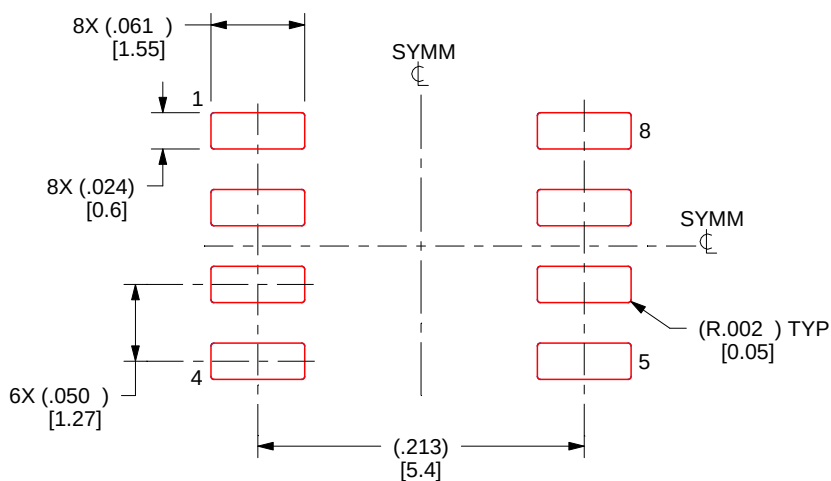
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

## EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## 重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
版权所有 © 2025，德州仪器 (TI) 公司